

Cotunneling signatures of Spin-Electric coupling in frustrated triangular molecular magnets

J.F. Noss^{1,2} and C.M. Canali¹

¹*Department of Physics and Electrical Engineering,
Linnaeus University, SE-39182 Kalmar, Sweden*

²*Solid State Physics/The Nanometer Structure Consortium,
Lund University, Box 118, SE-221 00 Lund Sweden*

(Dated: February 26, 2022)

The ground state of frustrated (antiferromagnetic) triangular molecular magnets is characterized by two total-spin $S = 1/2$ doublets with opposite chirality. According to a group theory analysis [M. Trif *et al.*, Phys. Rev. Lett. **101**, 217201 (2008)] an external electric field can efficiently couple these two chiral spin states, even when the spin-orbit interaction (SOI) is absent. The strength of this coupling, d , is determined by an off-diagonal matrix element of the dipole operator, which can be calculated by *ab-initio* methods [M. F. Islam *et al.*, Phys. Rev. B **82**, 155446 (2010)]. In this work we propose that Coulomb-blockade transport experiments in the cotunneling regime can provide a direct way to determine the spin-electric coupling strength. Indeed, an electric field generates a d -dependent splitting of the ground state manifold, which can be detected in the inelastic cotunneling conductance. Our theoretical analysis is supported by master-equation calculations of quantum transport in the cotunneling regime. We employ a Hubbard-model approach to elucidate the relationship between the Hubbard parameters t and U , and the spin-electric coupling constant d . This allows us to predict the regime in which the coupling constant d can be extracted from experiment.

I. INTRODUCTION

Molecular magnets (MMs)¹ represent a rich playground for exploring quantum mechanics at the nanoscale, and are intensively investigated both in condensed matter physics and chemistry. MMs, rationally designed and realized by chemical engineering,² are promising building blocks of electronic devices for molecular spintronics,^{3,4} and for classical⁵ and quantum information processing.^{6–8} For applications in quantum computation, MMs with frustrated antiferromagnetic coupling between spins are particularly promising, since at low energies they behave effectively as magnetic two-level systems with long spin coherent times, which can be used as qubits to encode and manipulate quantum information.^{2,8} One outstanding issue in quantum information processing is the need of realizing fast control and switching between quantum spin states. Standard spin-control techniques such as electron spin resonance (ESR), carried out by time dependent magnetic fields, have limitations, since in practice it is difficult to achieve switching times of the order of nanoseconds for large enough fields. The need to achieve spatial resolutions of the order of 1 nm represents another serious challenge for spin manipulations via magnetic fields. For these reasons, control via electric fields seems to be a much more promising alternative, since strong electric fields can be switched on and off fast, and applied selectively to nanoscale regions.^{9–11}

Electric control and manipulation of magnetic properties is an important topic in solid state physics, presently studied in multiferroic materi-

als, dilute magnetic semiconductors and topological insulators. The electric control of nanomagnets presents both hard challenges and novel possibilities. Since electric fields do not couple directly to spins, electric control can typically occur only indirectly, e.g., via a manipulation of the spin-orbit interaction (SOI). Indeed, interesting spin-electric effects induced solely by SOI have been realized in semiconductor quantum dots.¹² The applicability of this procedure in MMs on the other hand is much harder, since the relative strength of the SOI scales with the volume of the system, implying that impractically large electric fields are required for systems of the order of a few nanometers. Therefore alternative schemes for efficient spin-electric coupling in MMs have been proposed. One example relies on the electric manipulation of the spin exchange constant^{13,14} which can trigger various level crossings between magnetic states of a different total spin. Here we are interested in another type of spin-electric coupling, made it possible in certain antiferromagnetic MMs by the lack of inversion symmetry, as proposed by Trif *et al.*¹⁵ It turns out that in some of these antiferromagnetic molecules, such as the triangular $\{\text{Cu}_3\}$ and $\{\text{V}_3\}$ MMs,^{16,17} and other odd-spin rings, an electric field can couple spin states through a combination of exchange and chirality of the spin-manifold ground state (GS). For triangular MMs this coupling is nonzero even in the absence SOI.

The low-energy physics of a triangular MM can be described by three identical $1/2$ -spin Cu cations, located at $\mathbf{r}_j$, $j = 1, 2, 3$, interacting via an antiferromagnetic (Heisenberg) exchange coupling (see Fig. 1). The ground state consists of two

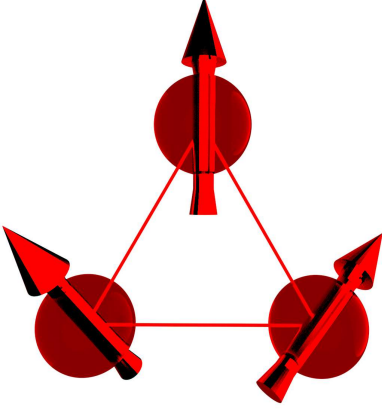


FIG. 1. Schematic representation of a triangular molecule.

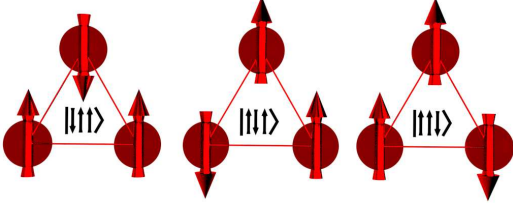


FIG. 2. The three independent spin configurations associated with total spin projection $S_z = 1/2$. The two chiral ground states $|E'_\pm, S_z = 1/2\rangle$ are linear combinations of these states.

total-spin $S = 1/2$ doublets, $|E'_\pm, S_z = \pm 1/2\rangle$, of opposite spin chirality, $E'_\pm$, which are degenerate in the absence of spin-orbit interaction. (Here E' refers to the two-dimensional irreducible representation (IR) of the D_{3h} symmetry group of the triangular MM, spanned by the two states, $|E'_+, S_z\rangle$ and $|E'_-, S_z\rangle$.) The states $|E'_\pm, S_z = 1/2\rangle$ can be written as linear combinations of the three frustrated spin configurations shown in Fig. 2.

According to an analysis based on group theory,^{15,18} the matrix elements of the components of the operator $\mathbf{R} = \sum_{j=1}^3 \mathbf{r}_j$ in the triangular molecule plane, $X_\pm = \pm X + iY$, between states of opposite chirality, do not vanish

$$e\langle E'_+, S_z | X_- | E'_-, S_z \rangle = e\langle E'_-, S_z | X_+ | E'_+, S_z \rangle = 2id. \quad (1)$$

In Eq. (1) e is the electron charge, $i = \sqrt{-1}$, and the real number d has the units of an electric dipole moment. All the other matrix elements of $\mathbf{R}$ in the subspace spanned by $\{|E'_\pm, S_z = \pm 1/2\rangle\}$ are zero. The nonzero value of d is in fact related to the existence of a nonzero electric dipole moment in each of the three frustrated spin configurations of Fig. 2 that compose the chiral ground states.^{19–22}

An electric field $\boldsymbol{\varepsilon}$ couples to the triangular MM via $e\boldsymbol{\varepsilon} \cdot \mathbf{R}$. Then the non-zero matrix elements in Eq. (1) ensure that the amplitude of the spin-electric coupling between chiral states is *linear*

in the field. Note that the electric-field-induced transitions conserve the total spin. However, in the presence of an additional small dc magnetic field that mixes the spin states, this spin-electric coupling can generate efficient electric transitions from one spin state to another.

The relevance of this spin-electric mechanism for qubit manipulation and qubits coupling clearly depends on the value of the electric dipole moment d . It has been proposed¹⁵ that an experimental estimate of d can in principle be provided by ESR measurements in static electric fields. Nuclear magnetic resonance, magnetization and specific heat measurements have also been proposed to determine the strength of the coupling experimentally.¹⁸ As far as we know these measurements have not yet been performed. Theoretically, a Hubbard model approach can provide understanding and a rough estimate of d in terms of a small number of Hubbard model parameters.¹⁸

In practice, a microscopic evaluation of d can only be provided by first-principles calculations. In fact, in Ref. 21 we have carried out Density Functional Theory (DFT) studies of a $\{\text{Cu}_3\}$ MM, and shown that d is of the order of $e10^{-4}a$, where a is the Cu-Cu separation. At electric fields of the order of 10^8 V/m, easily accessible in the vicinity of a scanning tunneling spectroscopy (STM) tip, a d of this size would ensure transition times of the order of 1 ns. More recent DFT calculations²³ have shown that the value of d in other triangular molecules, such as $\{\text{V}_3\}$ $\{\text{Cu}_3\text{O}_3\}$ and $\{\text{V}_{15}\}$, can be one or two orders of magnitude larger than in $\{\text{Cu}_3\}$.

In this paper we carry out a theoretical study of quantum transport through an *individual* triangular antiferromagnetic MM displaying the spin-electric coupling, arranged in a single-electron transistor (SET) geometry. The main motivation of this work is to investigate whether the coherent coupling of the two spin chiral states induced and controlled by an electric field has detectable consequences on the transport properties of the MM. Our conclusion is that, in the cotunneling regime of Coulomb blockade transport, the GS energy splitting induced by the electric field should be easily accessible and should provide a direct estimate of the strength of the electric dipole moment parameter d . In this coherent regime, higher excited states of the MM could add as additional auxiliary states that can be exploited to perform quantum gates.¹⁵ We also show that similar results could be obtained by performing inelastic electron tunneling spectroscopy through the MM adsorbed on surface by means of STM techniques. For the modeling of the MM we use the Hubbard model approach introduced in Ref. 18. This approach is quite convenient and transparent to address the effect of an applied electric field on the molecular

orbitals of the molecule leading to the spin-electric coupling. The parameters of the model are extracted from our previous first-principles calculations on $\{\text{Cu}_3\}$. Quantum transport is studied by means of a quantum master equation including both sequential and cotunneling contributions. Transport studies on triangular systems using a similar formalism have been done recently.^{24–29} But our motivation is different and an analysis of the spin-electric effect in this system has not been considered so far.

The paper is divided into the following four sections. In Sec. II we introduce a Hubbard approach to model the effect of the electric field leading to the spin-electric coupling in terms of a few free parameters. In Sec. III we introduce the model and the formalism to study quantum transport and calculate the conductance in the sequential tunneling and cotunneling regime. In Sec. IV we present transport results. Finally, we summarize the conclusions of our work in Sec. V

II. HUBBARD MODEL APPROACH TO THE SPIN-ELECTRIC COUPLING

In this section we introduce the Hubbard model approach developed in Ref. 18 to analyze the spin-electric coupling. This approach is very useful for three reasons. Firstly, it describes the effect of the applied electric field on the orbital degrees of freedom of the molecular magnet (MM), and therefore it elucidates the emergence of the spin-electric coupling at the microscopic level. Secondly, it permits the description of the spin-electric coupling in terms of a few parameters that can be evaluated by first-principles methods. Last but not least, it provides the natural framework to study later on quantum transport.

Before we introduce the Hubbard model, it is convenient to summarize the main results of the spin-electric coupling using the language of a spin Hamiltonian,¹⁵ in part already anticipated in the introduction, which will then emerge again from the Hubbard model.

The ground-state manifold of a three-site spin $s = 1/2$ Heisenberg antiferromagnet, with isotropic exchange constant J , is given by the two doubly-degenerate chiral doublets

$$|E'_\pm, S_z = \frac{1}{2}\rangle = \frac{1}{\sqrt{3}}(|\downarrow\uparrow\uparrow\rangle + \epsilon_\pm |\uparrow\downarrow\uparrow\rangle + \epsilon_\mp |\uparrow\uparrow\downarrow\rangle), \quad (2)$$

where $\epsilon_\pm = \exp(\pm 2\pi i/3)$. These states are eigenstates of the total spin $\mathbf{S}^2$ with eigenvalue $S = 1/2$, and of the total z component S_z , with eigenvalue $1/2$. The three spin configurations in Eq. (2) are shown in Fig. 2). Similar linear combinations can be written for the 2 eigenstates of S_z with eigen-

value $1/2$. These states are also eigenstates of the z -component of the chiral spin operator

$$C_z = \frac{4}{\sqrt{3}} \mathbf{s}_1 \cdot \mathbf{s}_2 \times \mathbf{s}_3, \quad (3)$$

with eigenvalue ± 1 . (The $\pm$ in $E'_\pm$ refers to this quantum number.)

The lowest excited state, separated from the ground state (GS) by an energy of order J , is the fourfold degenerate eigenstate of $\mathbf{S}^2$, with eigenvalue $3/2$. The element of this quartet that is an eigenstate of S_z with eigenvalue $1/2$, is written in terms of the same three spin configurations of Fig. 2 as

$$|A'_1, S_z = \frac{1}{2}\rangle = \frac{1}{\sqrt{3}}(|\downarrow\uparrow\uparrow\rangle + |\uparrow\downarrow\uparrow\rangle + |\uparrow\uparrow\downarrow\rangle). \quad (4)$$

The four states $|A'_1, S_z\rangle$ form four A'_1 one-dimensional IR of the symmetry group D_{3h} . Note that the expectation value of C_z for the states $|A'_1, S_z\rangle$ vanishes.

The SOI-induced Dzyaloshinskii-Moriya (DM) interaction splits the chiral GS manifold into two two-dimensional subspaces. As we discussed in the introduction, an electric field couples states of opposite chirality. These two interactions can be represented by the following low-energy effective spin Hamiltonian¹⁵

$$H_{\text{eff}}^{\text{spin}} = \Delta_{\text{SOI}} C_z S_z + d\mathbf{E} \cdot \mathbf{C}_\parallel \quad (5)$$

where $\mathbf{C}_\parallel \equiv (C_x, C_y, 0)$ is the component of the chiral operator in the xy plane. In Eq. (5) the energy Δ_{SOI} is proportional to the SOI coupling strength, and turns out to be equivalent to the DM coupling constant D . The parameter d is the electric dipole moment introduced in Eq. (1). We will now see how this effective spin Hamiltonian emerges from the Hubbard model approach.¹⁸

The second quantized one-band Hubbard Hamiltonian reads

$$H_U = - \sum_{i,j} \sum_{\alpha} \left\{ t_{ij} c_{i\alpha}^\dagger c_{j\alpha} + \text{h.c.} \right\} + \frac{1}{2} U \sum_i n_{i\uparrow} n_{i\downarrow}, \quad (6)$$

where $c_{i\alpha}^\dagger$ ($c_{i\alpha}$) creates (destroys) an electron with spin α at site i , $n_{i\alpha} = c_{i\alpha}^\dagger c_{i\alpha}$ is the particle number operator and t_{ij} is a spin-independent hopping parameter. More precisely, the index i labels a Wannier function localized at site i . The first term represents the kinetic energy describing electrons hopping between nearest-neighbor sites i and j . For D_{3h} symmetry this term is characterized by a hopping parameter $t_{ij} = t$. The second term is an on-site repulsion energy of strength U , which describe the energy cost associated with having two electrons of opposite spin on the same site. In this model the interaction energy between

electrons which are not on the same site is completely neglected. The Hubbard model is the simplest model describing the fundamental competition between the kinetic energy and the interaction energy of electrons on a lattice.

The spin-orbit interaction in the Hubbard model is described by adding the following spin-dependent hopping term^{18,30–32}

$$H_{\text{SOI}} = \sum_{i,j} \sum_{\alpha,\beta} \left\{ c_{i\alpha}^\dagger \left(i \frac{\mathbf{P}_{ij}}{2} \cdot \boldsymbol{\sigma}_{\alpha\beta} \right) c_{j\beta} + \text{h.c.} \right\}, \quad (7)$$

where $\boldsymbol{\sigma} = \sigma_x \hat{x} + \sigma_y \hat{y} + \sigma_z \hat{z}$ is the vector of the three Pauli matrices. A commonly used notation for the Pauli matrices is to write the vector index i in the superscript, and the matrix indices as subscripts, so that the element in row α and column β of the i th Pauli matrix is $\sigma_{\alpha\beta}^i$, with $i = x, y, z$. Here the vector $\mathbf{P}_{ij}$ is proportional to the matrix element of $\nabla V \times \mathbf{p}$ between the orbital parts of the Wannier functions at sites i and j ; V is the one-electron potential and $\mathbf{p}$ is the momentum operator. Clearly the spin-orbit term has the form of a spin-dependent hopping, which is added to the usual spin-independent hopping proportional to t . In Eq. (7), spin-orbit coupling induces a spin precession about $\mathbf{P}_{ij}$ when an electron hops from site i to site j . This form of the spin-orbit interaction is a special case of Moriya's hopping terms³³ in the limit that all but one orbital energy is taken to infinity,³¹ and it is consistent with our choice of a one-band Hubbard model. The x and y components of $\mathbf{P}_{ij}$ describe processes with different spin, and because of the α_v symmetry, $\mathbf{P}_{ij} = p\mathbf{e}_z$. Therefore, because of the symmetry of the molecule, the free Hubbard parameters are reduced to three, namely, t , U and p .

The final expression of the Hamiltonian describing the electrons in a triangular molecule, including the spin-orbit interaction, is

$$H_{U+\text{SOI}} = \sum_{i,\alpha} \left\{ c_{i\alpha}^\dagger (-t + i\lambda_{\text{SOI}}\alpha) c_{i+1\alpha} + \text{h.c.} \right\} + \sum_{i,\alpha} \left(\epsilon_0 n_{i\alpha} + \frac{1}{2} U n_{i\alpha} n_{i\bar{\alpha}} \right), \quad (8)$$

where $\lambda_{\text{SOI}} \equiv p/2 = \mathbf{P}_{ij}/2 \cdot \mathbf{e}_z$ is the spin-orbit parameter, ϵ_0 is the on-site orbital energy, and $\bar{\alpha} = -\alpha$.

We want to treat the two hopping terms perturbatively on the same footing, by doing an expansion around the atomic limit t/U , $\lambda_{\text{SOI}}/U \rightarrow 0$. In many molecular magnets $t \gg \lambda_{\text{SOI}}$. This turns out to be the case also for $\{\text{Cu}_3\}$.³⁴ In other molecules the two hopping parameters are of the same order of magnitude.

We are interested in the half-filled regime. From second-order perturbation theory in t/U , an antiferromagnetic isotropic exchange term emerges

and it splits the spin degeneracy of the low-energy sector of the Hubbard model, which is defined by the singly-occupied states.

The perturbative method requires the definition of the unperturbed states being the one-electron states

$$|\phi_i^\alpha\rangle = c_{i\alpha}^\dagger |0\rangle, \quad (9)$$

singly-occupied three-electron states

$$|\psi_i^\alpha\rangle = \prod_{j=1}^3 c_{j\alpha_j}^\dagger |000\rangle = \prod_{j=1}^3 |\phi_j^{\alpha_j}\rangle, \quad (10)$$

with $\alpha_j = \alpha$ for $j \neq i$ and $\alpha_j = \bar{\alpha}$, for $j = i$. Finally the doubly-occupied three-electron states

$$|\psi_{ij}^\alpha\rangle = c_{i\uparrow}^\dagger c_{i\downarrow}^\dagger c_{j\alpha}^\dagger |000\rangle, \quad (11)$$

with $i = 1, 2, 3$ and $j \neq i$. Note that the states in Eqs. (9)-(11) are eigenstates of the Hamiltonian, Eq. (8), only in the absence of the hopping and spin-orbit parameter and with energies ϵ_0 , $3\epsilon_0$ and $3\epsilon_0 + U$, respectively. These states are not yet symmetry adapted states of the D_{3h} point group. Symmetry adapted states can be found using the the projector operator formalism.^{18,35} One-electron symmetry adapted states can be written as a linear combinations of one-electron states, Eq. (9),

$$|\Phi_{A'_1}^\alpha\rangle = \frac{1}{\sqrt{3}} \sum_{i=1}^3 |\phi_i^\alpha\rangle, \quad (12)$$

and

$$|\Phi_{E'_\pm}^\alpha\rangle = \frac{1}{\sqrt{3}} \sum_{i=1}^3 \epsilon_{1,2}^{i-1} |\phi_i^\alpha\rangle, \quad (13)$$

where A'_1 and $E'_\pm$ are one-dimensional and two-dimensional IR in the D_{3h} point group, respectively, and $\epsilon^k = \exp((2\pi i/3)^k)^{1,2}$ is a phase factor. The three-electron symmetry adapted states for singly-occupied magnetic centers can be written as

$$|\psi_{A'_1}^{1\alpha}\rangle = \frac{1}{\sqrt{3}} \sum_{i=1}^3 |\psi_i^\alpha\rangle, \quad (14)$$

and

$$|\psi_{E'_\pm}^{1\alpha}\rangle = \frac{1}{\sqrt{3}} \sum_{i=1}^3 \epsilon_{1,2}^{i-1} |\psi_i^\alpha\rangle, \quad (15)$$

The states $|\psi_{E'_+}^{1\alpha}\rangle$ and $|\psi_{E'_-}^{1\alpha}\rangle$ have total spin $S = 1/2$ and z -spin projection $S_z = \pm 1/2$. These states are formally identical to the chiral states given in the Eq. (2), and are eigenstates of the Hubbard Hamiltonian when $t = \lambda_{\text{SOI}} = 0$. The

tunneling and spin orbit interaction (SOI) mix the singly-occupied and doubly-occupied states. Symmetry properties of the D_{3h} point group dictate that the tunneling and SOI terms in the Hubbard Hamiltonian transform as the irreducible (IR) A'_1 . Therefore, only states transforming according to the same IR could be mixed. The first-order correction in t/U and λ_{SOI}/U is obtained by mixing in doubly-occupied states¹⁸

$$|\Phi_{E'_\pm}^{1\alpha}\rangle \equiv |\psi_{E'_\pm}^{1\alpha}\rangle + \frac{(\epsilon_2^1 - 1)(t \pm \alpha\lambda_{\text{SOI}})}{\sqrt{2}U} |\psi_{E'_\pm}^{2\alpha}\rangle + \frac{3\epsilon_1^1(t \pm \alpha\lambda_{\text{SOI}})}{\sqrt{2}U} |\psi_{E'_\pm}^{2\alpha}\rangle, \quad (16)$$

where

$$|\psi_{E'_\pm}^{2\alpha}\rangle = \frac{1}{\sqrt{6}} \sum_{i=1}^3 \epsilon_{1,2}^{i-1} (|\psi_{i1}^\alpha\rangle + |\psi_{i2}^\alpha\rangle), \quad (17)$$

and

$$|\psi_{E'_\pm}^{2\alpha}\rangle = \frac{1}{\sqrt{6}} \sum_{i=1}^3 \epsilon_{1,2}^{i-1} (|\psi_{i1}^\alpha\rangle - |\psi_{i2}^\alpha\rangle), \quad (18)$$

are three-electron symmetry adapted states for doubly-occupied magnetic centers.

In the small t/U , λ_{SOI}/U limit, we can resort to a spin-only description of the low-energy physics of the system. The ground state manifold (corresponding to the states in Eq. (16)) is given by the two chiral spin states of Eq. (2). In this low-energy regime, the orbital states correspond to the singly-occupied localized atomic orbitals. The lowest energy states have total spin $S = 1/2$ and chirality $C_z = \pm 1$. Using the same perturbative procedure, we can construct approximate Hubbard model states corresponding to the $S = 3/2$ excited-state quartet of Eq. (4). To first order in t/U and λ_{SOI}/U one obtains

$$|\Phi_{A'_1}^{1\alpha}\rangle = |\psi_{A'_1}^{1\alpha}\rangle \quad (19)$$

The energy of the $S = 3/2$ quartet is $3J/2$ higher in energy than the energy of the chiral GS doublets, with $J \approx 4t^2/U$.

We now introduce the effect of the external electric field. An external electric field $\boldsymbol{\varepsilon}$ can couple to the molecule via two mechanisms. The first mechanism that we will study is by the modification of the on-site energies ϵ_0 via the Hamiltonian

$$H_{d-\varepsilon}^0 = \sum_{\alpha} \sum_{i=1}^3 (-e\mathbf{r}_i \cdot \boldsymbol{\varepsilon}) c_{i\alpha}^\dagger c_{i\alpha}, \quad (20)$$

where $\mathbf{r}_i$ is the coordinate vector of the i th magnetic center. From Fig. 3, the on-site electric Hamiltonian can be written as

$$H_{d-\varepsilon}^0 = -ea \sum_{\alpha} \left[\frac{\varepsilon^y}{\sqrt{3}} c_{1\alpha}^\dagger c_{1\alpha} - \frac{1}{2} \left(\varepsilon^x + \frac{\varepsilon^y}{\sqrt{3}} \right) c_{2\alpha}^\dagger c_{2\alpha} + \frac{1}{2} \left(\varepsilon^x - \frac{\varepsilon^y}{\sqrt{3}} \right) c_{3\alpha}^\dagger c_{3\alpha} \right], \quad (21)$$

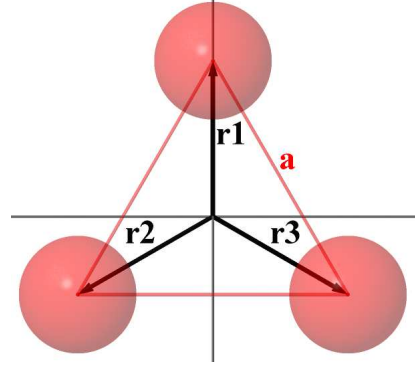


FIG. 3. Coordinates of magnetic centers in a triangular molecule. $\mathbf{r}_i$ is the coordinate of the i th electron.

where $\varepsilon^{x,y}$ are the in-plane coordinates of the electric field, e the electron charge and a the distance between magnetic centers.

The second mechanism is given by the modification of the hopping parameters t_{ii+1} and it can be written as

$$H_{d-\varepsilon}^1 = \sum_{\alpha} \sum_{i=1}^3 t_{ii+1,\alpha}^\varepsilon c_{i\alpha}^\dagger c_{i+1\alpha} + \text{H.c.}, \quad (22)$$

where $t_{ii+1,\alpha}^\varepsilon = \langle \phi_i^\alpha | -e\mathbf{r} \cdot \boldsymbol{\varepsilon} | \phi_{i+1}^\alpha \rangle$ are the modified hopping parameters due to the external electric field $\boldsymbol{\varepsilon}$, ϕ_i^α are the Wannier states localized on the i th magnetic center with spin α . These induced hopping parameters can be written as $t_{ii+1,\alpha}^\varepsilon = \sum_q q_{ii+1}^\alpha \varepsilon_q$, with $q_{ii+1}^\alpha = -e \langle \phi_i^\alpha | q | \phi_{i+1}^\alpha \rangle$ and $q = x, y, z$. D_{3h} point group symmetry properties, given by the dipole selection rules, reduce the number of free parameters induced by the electric field. Finding these free parameters is not an easy task when the basis set is composed of localized Wannier orbitals. In order to investigate the effect of the electric field on the triangular molecule, we switch from the localized Wannier basis set to the symmetry adapted basis set $\Gamma = A'_1, E'_\pm$. Then we apply the transition dipole selection rules to the new induced hopping parameters. In the symmetry adapted states, the hopping-Hamiltonian, Eq. (22), reads

$$H_{d-\varepsilon}^1 = \sum_{\alpha} \sum_{\Gamma\Gamma'} t_{\Gamma,\Gamma',\alpha}^\varepsilon c_{\Gamma\alpha}^\dagger c_{\Gamma'\alpha} + \text{H.c.}, \quad (23)$$

where $\Gamma, \Gamma' = A'_1, E'_+, E'_-,$ $t_{\Gamma,\Gamma',\alpha}^\varepsilon = \sum_q q_{\Gamma\Gamma'}^\alpha \varepsilon_q$, with $q = x, y, z$ and $q_{\Gamma\Gamma'}^\alpha = -e \langle \phi_\Gamma^\alpha | q | \phi_{\Gamma'}^\alpha \rangle$. Here $c_{\Gamma\alpha}^\dagger (c_{\Gamma\alpha})$ creates (destroys) an electron in the adapted state Γ with spin α . Note that in Eq. (23) all the possible transitions are included, even those between states of the same symmetry adapted basis set. Dipole transition rules then will select the allowed transitions and the corresponding states. Although symmetry properties control the dipole transition rules, they do not allow us to calculate

the strength of the transitions. Detailed experimental measurements and/or accurate *ab-initio* calculations have to be carried out to determine them. In the D_{3h} point group, the (x, y) and z -coordinates span as the E' and the A'_1 IR, respectively. We have grouped x and y because they form a degenerate pair within the E' representation. From character tables of the D_{3h} point group, the only allowed transitions correspond to

$$\begin{aligned} \langle \phi_{E'_+}^\alpha | x | \phi_{E'_-}^\alpha \rangle &= -i \langle \phi_{E'_+}^\alpha | y | \phi_{E'_-}^\alpha \rangle \equiv -\frac{d_{EE}}{e} \\ \langle \phi_{A'_1}^\alpha | x | \phi_{E'_+}^\alpha \rangle &= -i \langle \phi_{A'_1}^\alpha | y | \phi_{E'_+}^\alpha \rangle \equiv -\frac{d_{AE}}{e} \\ \langle \phi_{A'_1}^\alpha | x | \phi_{E'_-}^\alpha \rangle &= i \langle \phi_{A'_1}^\alpha | y | \phi_{E'_-}^\alpha \rangle \equiv -\frac{d_{AE}}{e} \end{aligned} \quad (24)$$

where d_{EE} and d_{AE} are the only two free parameters to be determined. Here we have used the symmetry rule that the product $f_1 \otimes f_2 \otimes f_3 \neq 0$ if it spans the A_1 representation. All the other possible transitions are not allowed within the D_{3h} symmetry group. Inserting these allowed transitions into the Hamiltonian, Eq. (23), we have¹⁸

$$\begin{aligned} H_{d-\epsilon}^1 &= \sum_{\alpha} \left[d_{AE} \left(\bar{\mathcal{E}} c_{A'_1\alpha}^\dagger c_{E'_-\alpha} + \mathcal{E} c_{A'_1\alpha}^\dagger c_{E'_+\alpha} \right) \right. \\ &\quad \left. + d_{EE} \bar{\mathcal{E}} c_{E'_-\alpha}^\dagger c_{E'_+\alpha} \right] + \text{H.c.}, \end{aligned} \quad (25)$$

where $\mathcal{E} = \epsilon^x + i\epsilon^y$ and $\bar{\mathcal{E}} = \epsilon^x - i\epsilon^y$. Note that the parameters d_{AE} and d_{EE} tell us about the possible dipole-electric transitions between states that span the A'_1 - $E'_\pm$ and $E'_+-E'_-$ IR, respectively. From Eq. (15) we can see that the chiral states also span the $E_\pm$ IR.

To take even more advantage of the symmetry of the triangular molecule, we now write the relationship between the second quantized operators $c_{i\alpha}^\dagger, c_{i\alpha}$ and the symmetry adapted operators $c_{\Gamma\alpha}^\dagger, c_{\Gamma\alpha}$. From Eqs. (9), (12) and (13), we have

$$\begin{pmatrix} c_{A'_1\alpha}^\dagger \\ c_{E'_+\alpha}^\dagger \\ c_{E'_-\alpha}^\dagger \end{pmatrix} = \begin{pmatrix} 1 & 1 & 1 \\ 1 & \epsilon & \epsilon^2 \\ 1 & \epsilon^2 & \epsilon \end{pmatrix} \begin{pmatrix} c_{1\alpha}^\dagger \\ c_{2\alpha}^\dagger \\ c_{3\alpha}^\dagger \end{pmatrix}, \quad (26)$$

where we have used $\epsilon^4 = \epsilon$. From the last equation we can write the localized second quantized operators as a linear combination of symmetry adapted operators

$$\begin{pmatrix} c_{1\alpha}^\dagger \\ c_{2\alpha}^\dagger \\ c_{3\alpha}^\dagger \end{pmatrix} = \begin{pmatrix} 1 & 1 & 1 \\ 1 & \epsilon^2 & \epsilon \\ 1 & \epsilon & \epsilon^2 \end{pmatrix} \begin{pmatrix} c_{A'_1\alpha}^\dagger \\ c_{E'_+\alpha}^\dagger \\ c_{E'_-\alpha}^\dagger \end{pmatrix}. \quad (27)$$

Now we can write the rest of the perturbed Hamiltonian, namely the $H_{d-\epsilon}^0$ on-site electric field Hamiltonian (Eq. (21)) and H_{SOI} spin-orbit

Hamiltonian (Eq. (7)), in terms of the symmetry adapted operators

$$\begin{aligned} H_{d-\epsilon}^0 &= -\frac{iae}{2\sqrt{3}} \sum_{\alpha} \left[\bar{\mathcal{E}} c_{E'_+\alpha}^\dagger c_{A'_1\alpha} - \mathcal{E} c_{E'_-\alpha}^\dagger c_{A'_1\alpha} \right. \\ &\quad \left. + \bar{\mathcal{E}} c_{E'_-\alpha}^\dagger c_{E'_+\alpha} \right] + \text{H.c.}, \end{aligned} \quad (28)$$

and

$$H_{\text{SOI}} = \sqrt{3} \lambda_{\text{SOI}} \sum_{\alpha} \alpha \left(c_{E'_-\alpha}^\dagger c_{E'_-\alpha} - c_{E'_+\alpha}^\dagger c_{E'_+\alpha} \right). \quad (29)$$

We conclude this section with the following important considerations

1. With the use of the symmetry properties of the triangular molecule, the Hubbard model in the presence of SOI (Eq. (29)) and an external electric field (Eqs. (25) and (28)), can be parametrized by five free parameters: $t, U, \lambda_{\text{SOI}}, d_{EE}$ and d_{AE} . For a realistic molecular magnet, $t, U, \lambda_{\text{SOI}}$ can be extracted from first-principles calculations, as for example done in Ref. 34 for $\{Cu_3\}$. An analogous determination of the single-particle parameters d_{EE} and d_{AE} has not been attempted so far. For localized orbitals, one expects $ea \gg d_{EE}, d_{AE}$, and this the assumption that we will make in the paper.

2. Eqs. (25) and (28) and Eq. (29) are completely consistent with the effective spin Hamiltonian result of Eq. (5), in that they imply a splitting of the chiral GS by the SOI, and a linear coupling of the same states by an electric field. Note also that the SOI does not mix states of different chirality and/or spin.

3. Clearly Eqs. (25) and (28) and Eq. (29) are single-particle Hamiltonian. In order to extract the electric-dipole moment d and the DM splitting Δ_{SOI} appearing in Eq. (5), one has to take matrix elements of these Hamiltonians between many-body states $|\Phi_{E'_\pm}^{1\alpha}\rangle$ defined in Eq. (16). For the matrix elements of the electric field Hamiltonian one finds¹⁸

$$\left| \langle \Phi_{E'_-}^{1\alpha} | H_{d-\epsilon}^0 | \Phi_{E'_+}^{1\alpha} \rangle \right| \simeq \left| \frac{t^3}{U^3} \mathcal{E} ea \right|, \quad (30)$$

$$\left| \langle \Phi_{E'_-}^{1\alpha} | H_{d-\epsilon}^1 | \Phi_{E'_+}^{1\alpha} \rangle \right| \simeq \left| \frac{4t}{U} \mathcal{E} d_{EE} \right|. \quad (31)$$

It follows that the electric-dipole moment d of the spin electric coupling is given by a combination of $\left| \frac{t^3}{U^3} ea \right|$ and $\left| \frac{4t}{U} d_{EE} \right|$.

4. In the presence of an electric field, the degenerate GS chiral manifold $\{|\Phi_{E'_\pm}^{1\alpha}\rangle\}$ is replaced by the coherent linear superpositions

$$|\chi_{\pm}^{\alpha}(\epsilon)\rangle = \frac{1}{\sqrt{2}} \left(|\Phi_{E'_+}^{1\alpha}\rangle + \pm \frac{|\mathbf{d} \cdot \boldsymbol{\epsilon}|}{\mathbf{d} \cdot \boldsymbol{\epsilon}} |\Phi_{E'_-}^{1\alpha}\rangle \right) \quad (32)$$

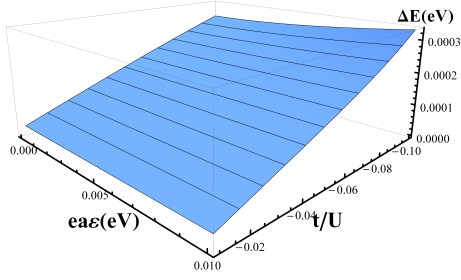


FIG. 4. (Color online) Electric-field-induced splitting $\Delta E(\varepsilon)$ of the chiral ground state energy for a triangular molecular magnet at half-filling ($N = 3$), as a function of field strength ε and t/U . At these small/moderate values of the field, $\Delta E(\varepsilon)$ depends linearly on ε .

with energies

$$E_{\pm}(\varepsilon) = E_{\pm}(0) \pm d\varepsilon/\sqrt{2} \quad (33)$$

Note that spin degeneracy is preserved, even when SOI is included. The electric-field-induced splitting of the chiral GS, $\Delta E(\varepsilon) \equiv E_+(\varepsilon) - E_-(\varepsilon)$, is proportional to ε , at least in this approximation, in agreement with the effective spin Hamiltonian approach. We will refer to the states $|\chi_{\pm}^{\alpha}(\varepsilon)\rangle$ as *mixed chiral states*. They will play a crucial role in transport.

5. Eqs. (25) and (28) show that an electric field, in fact, can couple $\{|\Phi_{E_{\pm}}^{1\alpha}\rangle\}$ with $|\Phi_{A_2}^{1\alpha}\rangle$. However this coupling, which in principle could affect Eq. (32) is not important, since these states are separated by an energy of order J . We will therefore disregard it.

In Figs. 4 and 5 we plot the computed energy splitting of the chiral GS, $\Delta E(\varepsilon)$, induced by an electric field of strength ε , as a function of ε and t/U . The splitting is, as expected, linear in ε at small fields. This is the landmark of the spin-electric coupling. However, at larger field, we find also a quadratic dependence. It seems that, despite the large value of U , the system has a sizable polarizability, leading to an rather strong induced electric dipole moment in the presence of a field. This is responsible for the quadratic contribution in $\Delta E(\varepsilon)$.

All the calculations on the model presented in the next section are obtained by exact diagonalization of the Hubbard model for $N = 2, 3, 4$ filling or *charge states*. It turns out, however, that for the values of the parameters relevant for $\{Cu_3\}$, the perturbative results in t/U are typically quite close to the exact results.

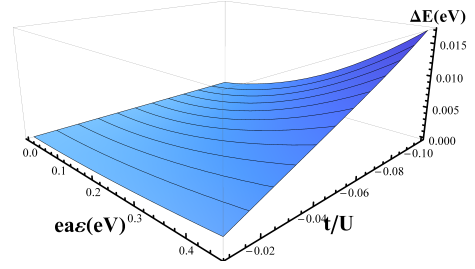


FIG. 5. (Color online) The same as in Fig. 4, but for larger values of the electric field, showing a quadratic dependence of $\Delta E(\varepsilon)$ due to an induced electric dipole moment.

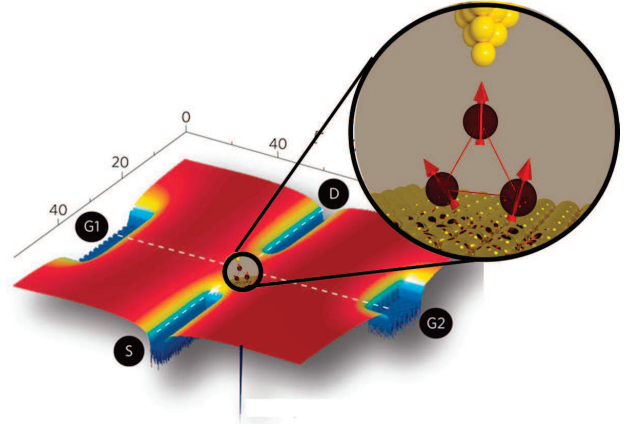


FIG. 6. Schematic representation of the transport geometry with a triangular molecular magnet. Picture modified from the original work by Fuechsle *et al.*. Reprinted by permission from Macmillan Publishers Ltd: Nature Nanotechnology 7, 242246, copyright (2012)

III. TRANSPORT MODEL AND MASTER EQUATION APPROACH

A. Transport setup

We are interested in studying quantum transport through a triangular molecular magnet (MM), weakly coupled to conducting leads, gated, and with the possibility of an extra external electric field for control of the spin-electric coupling. The transport regime that we have in mind is predominately controlled by Coulomb blockade physics. Later in this section we will also comment on the possibility of employing inelastic electric tunneling spectroscopy without the presence of charging effects.

A possible transport geometry is schematically shown in Fig. 6. The MM is placed on a surface (semiconducting or insulating.). Two conducting coplanar leads acting as source (S) and drain (D) are constructed on the surface, for example using techniques recently to realize a single-atom tran-

sistor.³⁶ The molecule is weakly coupled to S and D leads via ligands. Two in-plane gates (G1 and G2) are also patterned on either side of the transport channel. The orientation of the MM on the surface is such that the electric field from the gate is orthogonal to the plane of the MM, and it is simply used as a capacitive coupling to control the chemical potential of MM. Alternatively, S and D nanoleads and gate electrodes can be constructed by nano-lithography by depositing metal atoms (e.g., Au) on an insulating surface. Finally, a STM tip is positioned in the vicinity of the MM (see the blown-up region of the device close to the MM). This electrode is supposed to provide another *strong* and *localized* electric field to manipulate the MM states via the spin-electric coupling discussed in the previous section.

The construction of the device described here is very challenging. But we rely on recent progress in STM nano-lithography, and especially in functionalizing MMs on surfaces.

A second possibility is to study transport in a single-electron transistor (SET) built in more traditional molecular electronic device. MMs are presently being successfully investigated with this techniques.^{14,37,38} Here the challenge is to provide an independent extra gate electrode (besides the ordinary back gate) to reliably generate an in-plane electric field triggering the spin-electric coupling.

In the following we will assume that the following three features are present in our system: (i) source and drain leads weakly coupled to the molecule, providing a bias voltage V_b for electric transport; (ii) a gate voltage generating a variable potential V_g on the molecule able to manipulate its charge state; (iii) a third independent local electric field ϵ , of strengths typically attainable in the vicinity of a STM, with a component in the plane of the MM.

B. Hamiltonian of the transport device

The Hamiltonian of the system, schematically represented in Fig. 6, is the sum of three terms

$$\mathcal{H} = \mathcal{H}_{L/R} + \mathcal{H}_{\text{mol}} + \mathcal{H}_{L/R}^T, \quad (34)$$

where

$$\mathcal{H}_{L/R} = \sum_{k\alpha} \varepsilon_k^{L/R} a_{L/Rk\alpha}^\dagger a_{L/Rk\alpha} \quad (35)$$

describes free (*i.e.*, noninteracting) electrons in the left/right conducting lead (source/drain). Here, the operator $a_{L/Rk\alpha}^\dagger$ ($a_{L/Rk\alpha}$) creates (destroys) one electron with wave vector k and spin α in the left/right lead, respectively with energy $\varepsilon_k^{L/R}$.

The tunnel junctions representing the coupling between leads and MM are described by the tunneling Hamiltonian

$$\mathcal{H}_{L/R}^T = \sum_{km\alpha} \left(T_{km\alpha}^{L/R} a_{L/Rk\alpha}^\dagger c_{m\alpha} + \text{H.c.} \right), \quad (36)$$

where $T_{km\alpha}^{L/R}$ is the tunneling amplitude, $c_{m\alpha}^\dagger$ ($c_{m\alpha}$) creates (destroys) an electron in a single particle state with quantum numbers m and α inside the MM. The tunneling Hamiltonian $\mathcal{H}_{L/R}^T$ is treated as a perturbation to $\mathcal{H}_{\text{mol}}$ and $\mathcal{H}_{L/R}$.

The general form of the MM Hamiltonian is given by

$$\mathcal{H}_{\text{mol}} = \mathcal{H}_0 + \mathcal{H}_U + \mathcal{H}_t + \mathcal{H}_{\text{SOI}} + \mathcal{H}_{\text{EF}}, \quad (37)$$

where

$$\mathcal{H}_0 = \sum_j \sum_\alpha (\epsilon_j - e V_g) c_{j\alpha}^\dagger c_{j\alpha}, \quad (38)$$

with V_g the gate voltage. $\mathcal{H}_U = U \sum_j n_{j\uparrow} n_{j\downarrow}$ with U the on-site Coulomb repulsion parameter and $n_{j\alpha} = c_{j\alpha}^\dagger c_{j\alpha}$ the number operator. $\mathcal{H}_t = t \sum_j \sum_\alpha c_{j\alpha}^\dagger c_{j+1\alpha} + \text{H.c.}$ the hopping Hamiltonian with t the hopping parameter. $\mathcal{H}_{\text{EF}} = \mathcal{H}_{d-\epsilon}^1 + \mathcal{H}_{d-\epsilon}^0$ the electric field Hamiltonian defined in Eqs. (25) and (28) and $\mathcal{H}_{\text{SOI}}$ the spin-orbit Hamiltonian defined in Eq. (29).

We assume the Coulomb interaction between electrons in the MM and those in the environment, to be determined by a single and constant capacitance $C = C_L + C_R + C_g$, where $C_{L/R}$ and C_g are the capacitances of the right/left lead and the gate electrode, respectively. Another assumption is that the single-particle spectrum is independent of these interactions.

Quantum transport, e.g. the calculation of the tunneling conductance as a function of bias and gate voltages, can now be studied by means of a quantum master equation. General derivations of these equations have recently appeared in the literature,^{39–41} together with several approximate solutions applied to SETs with quantum dots⁴² and molecules,^{40,41,43} including MMs.^{39,44–47} The simplest strategy is to solve these equations perturbatively in the tunneling Hamiltonian.⁴⁸

C. Coulomb blockade Regime, Sequential Tunneling

In the regime of weak coupling between leads and molecule, transport occurs via the so-called sequential tunneling.⁴⁸ We review here the main characteristics of this regime an the steps leading to the calculation of the current.⁴⁸ In this regime the conductance of the tunnel junctions should

be much smaller than the quantum of conductance $\mathcal{G}_Q = 2e^2/h$. The electron tunneling rates Γ should be much smaller than the charging energy E_c of the molecule and the temperature: $\hbar\Gamma \ll k_B T \ll E_c$. The time between two tunneling events Δt is the longest time scale in the regime. In particular $\Delta t \gg \tau_\phi$, where τ_ϕ is the electron phase coherence. This guarantees that once the electron tunnels in, it has the time to loose its phase coherence before it tunnels out. Therefore the charge state can be treated classically and superposition of different charge states is not allowed. Only one-electron transitions between leads and molecule occur in the system. These transitions are characterized by rates Γ_{ij} , where i, j are the initial and final system states of the system involved in the electron transfer. The system is described by stationary non-equilibrium populations $\mathcal{P}_i$ of the state i . These occupation probabilities can be obtained from the master equation

$$\frac{d}{dt}\mathcal{P}_i = \sum_{j(j \neq i)} (\Gamma_{ij}\mathcal{P}_j - \Gamma_{ji}\mathcal{P}_i) . \quad (39)$$

The first RHS term represents events where the electron tunnels into the state i from the state j , while the second RHS term represents events where the electron tunnels out from the state i into the state j . These probabilities obey the normalization condition

$$\sum_i \mathcal{P}_i = 1 . \quad (40)$$

In the steady state, the probabilities are time-independent $d\mathcal{P}_i/dt = 0$. Therefore, Eq. (39) can be written as

$$0 = \frac{d}{dt}\mathcal{P}_i = \sum_{j(j \neq i)} (\Gamma_{ij}\mathcal{P}_j - \Gamma_{ji}\mathcal{P}_i) . \quad (41)$$

In the regime of sequential tunneling the transition amplitudes are computed by first-order perturbation theory in the tunneling Hamiltonian $\mathcal{H}^T$, Eq. (36). Therefore the transition rates from state i to state j , through the left/right lead, are given by Fermi's golden Rule

$$\Gamma_{i \rightarrow j}^{L/R} = \frac{2\pi}{\hbar} \sum_{i,j} \left| \langle j | H_{L/R}^T | i \rangle \right|^2 W_i \delta(E_j - E_i) , \quad (42)$$

where W_i is a thermal distribution function and $E_j - E_i$ gives the energy conservation. The states $|i\rangle$ and $|j\rangle$ are the unperturbed system states and are defined as a product of the molecule and lead states $|i\rangle = |i_{mol}\rangle \otimes |i_l\rangle \otimes |i_r\rangle$. Transition rates depend on whether an electron is leaving or entering the molecule through the left or right lead. Inserting the tunneling Hamiltonian Eq. (36) into

the Fermi's golden Rule, Eq. (42), the transition rates become^{48,49}

$$\Gamma_{i \rightarrow j}^{L/R,-} = \gamma_{ji}^{L/R,-} [1 - f_{L/R}(E)] , \quad (43)$$

$$\Gamma_{i \rightarrow j}^{L/R,+} = \gamma_{ji}^{L/R,+} [f_{L/R}(E)] , \quad (44)$$

where

$$\gamma_{ji}^{L/R,-} = \Gamma^{L/R} \sum_{m,\alpha} |\langle j | c_{m,\alpha} | i \rangle|^2 \quad (45)$$

and

$$\gamma_{ji}^{L/R,+} = \Gamma^{L/R} \sum_{m,\alpha} |\langle j | c_{m,\alpha}^\dagger | i \rangle|^2 \quad (46)$$

are the transition matrix elements between the states j and i of the molecule (we have now dropped the label "mol"); $E = E_j - E_i$ is the energy difference between molecule many-electron states, and $f_{L/R}(E) = [e^{(E - \mu_{L/R})/k_B T} + 1]^{-1}$ is the Fermi function. Here the combination between the tunneling amplitudes $T_{m,\alpha}^{L/R}$ and the left/right lead density of states $D_{L/R}(i_{L/R})$ is assumed to be constant: $\Gamma^{L/R} = (2\pi/\hbar) |T_{m,\alpha}^{L/R}|^2 D_{L/R}(i_{L/R}) = (2\pi/\hbar) |T^{L/R}|^2 D_{L/R}(i_{L/R})$. The full transition matrix in the master equation, Eq. (39) is the sum of all contributions of electrons tunneling out or into the molecule, Eqs. (43) and (44):

$$\Gamma_{ij} = \Gamma_{ij}^{L,+} + \Gamma_{ij}^{R,+} + \Gamma_{ij}^{L,-} + \Gamma_{ij}^{R,-} . \quad (47)$$

The stationary rate equation, Eq. (41), is a system of linear equations and has to be solved numerically for a system of n many-electron states that are taking into account. We can rewrite it as a matrix equation

$$0 = \sum_j^n \Lambda_{ij} \mathcal{P}_j , \quad (48)$$

where

$$\Lambda_{ij} = \Gamma_{ij} - \delta_{ij} \sum_{k=1}^n \Gamma_{kj} . \quad (49)$$

There must exist a physical solution to Eq. (48). Therefore we replace the first line of of this equation by the normalization condition, Eq. (40), fixing $\Lambda_{1j} = 1$. Thus we can write

$$\delta_{1i} = \sum_j^n \Lambda_{ij} \mathcal{P}_j \quad (50)$$

instead Eq. (48). Because Coulomb blockade is typically studied at low temperatures some transitions rates might become exponentially small. This leads to numerical problems in solving

Eq. (50). Then some of the states do not contribute and one has to develop a convenient truncation method.⁴⁵

Finally, the current flowing through left lead coming into the molecule must be equal to the current flowing through right lead coming out from the molecule. Knowing the occupation probabilities, Eq. (41), the current through the system is defined as⁴²

$$I \equiv I^{L/R} = (-/+)e \sum_{i,j(j \neq i)} \mathcal{P}_j \left(\Gamma_{ij}^{L/R,-} - \Gamma_{ij}^{L/R,+} \right) \quad (51)$$

This expression contains implicitly the bias and gate voltages. Therefore IV curves can be obtained for finite values of these voltages. The bias derivative of the current gives the differential conductance G . When plotted as a function of the bias V_b , the current has steps in correspondence of values of V_b at which new transitions involving two contiguous charge states are energetically allowed. At low voltages – smaller than the charging energy – this is not possible and the current is blocked. In correspondence of these transitions, the conductance as function of V_b displays peaks. When plotted simultaneously as a function of both V_b and V_g , the conductance displays a characteristic diamond pattern, the so-called stability diagram: inside each diamond a given charge state is stable and the current is blocked.

D. Cotunneling Regime

When the coupling to the leads becomes stronger the description of transport based on incoherent sequential tunneling is no longer enough. In particular higher-order tunneling processes in which the electron tunnels coherently through clas-

sically forbidden charge states. As a result, for values of the voltages where sequential tunneling predicts a blocking of the current, a small leakage current is in fact possible though these processes.⁴⁸ The simplest example of these processes is second order in the tunneling Hamiltonian, and it is known as cooperative tunneling or cotunneling. Typically for the cotunneling regime $k_B T < \hbar \Gamma \ll E_c$.

Cotunneling can be either elastic or inelastic. In the former case the energies of the initial and final state are the same, while in the latter the energies are different. Signatures for these processes have also been observed in single-molecule junctions.^{14,37,38} Beyond the sequential tunneling regime, the tunneling Hamiltonian must be replaced by the T -matrix, which is given by⁴⁸

$$T = \mathcal{H}^T + \mathcal{H}^T \frac{1}{E_j - \mathcal{H}_0 + i\eta} T, \quad (52)$$

where E_j is the energy of the initial state $|j\rangle|n\rangle$, where $|j\rangle$ refers to the equilibrium state on the left and right lead and $|n\rangle$ is the initial molecular state, $\eta = 0+$ is a positive infinitesimal and $\mathcal{H}_0 = \mathcal{H}_{mol} + \mathcal{H}_{L/R}$. To second order, the transition rates from state $|j\rangle|n\rangle$ to $|j'\rangle|n'\rangle$ with an electron tunneling from lead α to the lead α' are given by

$$\Gamma_{\alpha\alpha'}^{n;j;n'j'} = \frac{2\pi}{\hbar} \left| \langle j'| \langle n'| \mathcal{H}^T \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} \mathcal{H}^T | n \rangle | j \rangle \right|^2 \times \delta(E_{j'n'} - E_{jn}), \quad (53)$$

where $E_{j'n'}$ and E_{jn} are the energies of the final and initial states, respectively. Here $|j'\rangle|n'\rangle = a_{\alpha'\mathbf{k}'\sigma'}^\dagger a_{\alpha\mathbf{k}\sigma} |j\rangle|n\rangle$. Inserting the tunneling Hamiltonian, Eq. (36), in last equation and after some algebra (see Appendix A) one can get the expression for the transition rates for processes from lead α till lead α' and from molecular state $|n\rangle$ to the state $|n'\rangle$:

$$\Gamma_{\alpha\alpha'}^{n;n'} = \sum_{\sigma\sigma'} \gamma_{\alpha}^{\sigma} \gamma_{\alpha'}^{\sigma'} \int d\varepsilon f(\varepsilon - \mu_{\alpha}) (1 - f(\varepsilon + \varepsilon_n - \varepsilon_{n'} - \mu_{\alpha'})) \times \left| \sum_{n''} \left\{ \frac{A_{n''n'}^{\sigma*} A_{n''n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_{n''} + i\eta} + \frac{A_{n'n''}^{\sigma'} A_{nn''}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_{n''} + i\eta} \right\} \right|^2, \quad (54)$$

where σ is the electron spin, $f(\varepsilon)$ is the Fermi distribution function, μ_{α} is the chemical potential of the lead α , $\mu_L - \mu_R = -eV/2$, $|n''\rangle$ is a virtual state, $A_{ij}^{\sigma'} = \langle i | c_{\sigma'} | j \rangle$ and $A_{ij}^{\sigma*} = \langle j | c_{\sigma}^\dagger | i \rangle$. Here γ_{α}^{σ} is the tunneling amplitude. Note that $|n\rangle$ and $|n'\rangle$ are states with the same number of particles. We have not taken into account processes changing the electron number by ± 2 units.^{43,50}

The transition rates in Eq. (54) cannot be evaluated directly because of the second-order poles in the energy denominators. A regularization scheme has been carried out to fix these divergences and obtain the cotunneling rates.^{51,52} Here it is important to mention that these divergences are, in fact, an artifact of the T -matrix approach rather than a real physical problem. The fourth-order

Bloch-Redfield quantum master equation (BR) and the real-time diagrammatic technique (RT) approaches to quantum transport have been developed to avoid any divergences and therefore no *ad hoc* regularization to cotunneling is required.^{40,41} Nevertheless, the T -matrix approach agrees with

these two approaches and gives good reasonable results deep inside the Coulomb blockade region.⁴⁶ We expect to catch all the relevant physics for our system with the T -matrix approach. After the regularization scheme is implemented, we get the tunneling rates defined as (see Appendix B)

$$\Gamma_{\alpha\alpha'}^{n;n'} = \sum_{\sigma\sigma'} \gamma_{\alpha}^{\sigma} \gamma_{\alpha'}^{\sigma'} \left[\sum_k (A^2 J(E_1, E_2, \varepsilon_{ak}) + B^2 J(E_1, E_2, \varepsilon_{bk})) + 2 \sum_q \sum_{k \neq q} A_k A_q I(E_1, E_2, \varepsilon_{ak}, \varepsilon_{aq}) \right. \\ \left. + 2 \sum_q \sum_{k \neq q} B_k B_q I(E_1, E_2, \varepsilon_{bk}, \varepsilon_{bq}) + 2 \sum_q \sum_k A_k B_q I(E_1, E_2, \varepsilon_{ak}, \varepsilon_{bq}) \right] \quad (55)$$

where $A_k = A_{kn'}^{\sigma*} A_{kn}^{\sigma'}$, $B_k = A_{n'k}^{\sigma'} A_{nk}^{\sigma*}$, $\varepsilon_{ak} = \varepsilon_{n'} - \varepsilon_k$, $\varepsilon_{bk} = \varepsilon_k - \varepsilon_n$, $E_1 = \mu_{\alpha}$ and $E_2 = \mu_{\alpha'} + \varepsilon_{n'} - \varepsilon_n$. Here I and J are integrals that come out from the regularization scheme, and are defined in Eqs. (B1) and (B2), respectively.

The complete master equation, including both sequential and cotunneling contributions, finally reads

$$\frac{d}{dt} \mathcal{P}_i = \sum_{j(j \neq i)} (\Gamma_{ij} \mathcal{P}_j - \Gamma_{ji} \mathcal{P}_i) \\ + \sum_{\alpha\alpha'j} \left(\Gamma_{\alpha\alpha'}^{ji} \mathcal{P}_j - \Gamma_{\alpha\alpha'}^{ij} \mathcal{P}_i \right) \quad (56)$$

and the current through the system is now given by

$$I \equiv I^{L/R} = (-/+) e \sum_{i,j(j \neq i)} \mathcal{P}_j \left(\Gamma_{ij}^{L/R,-} - \Gamma_{ij}^{L/R,+} \right) \\ + (-/+) e \sum_{i,j(j \neq i)} \mathcal{P}_j \left(\Gamma_{LR/RL}^{ji} - \Gamma_{RL/LR}^{ij} \right) \quad (57)$$

As mentioned above, cotunneling gives rise to a small current inside a Coulomb-blockade diamond region of a given charge state. At small values of the bias voltage, smaller than any excitation energies for the given charge state, we are in the regime of *elastic cotunneling* and the current is proportional to the bias voltage. At voltages corresponding to the transition energy to the first excited state of the *same* charge state, a new cotunneling transport channel becomes available and the slope of the linear dependency of the current increases. This signals the first occurrence of *inelastic cotunneling*. Upon further increasing the bias, other upward changes of the slope of the current occur in correspondence to energies at which higher excited states become available. It follows that the differential conductance displays *steps* that resemble the IV curve in the sequential tunneling regime. Note however, that the nature of the two curves is very different: at low bias the conductance is finite (elastic cotunneling). Furthermore the width

of the steps in the cotunneling conductance gives the energy difference between states of the *same* charge state, fixed by the specific Coulomb diamond of the stability diagram. Therefore, cotunneling is an excellent tool to investigate *directly* the excitation energies of a given charge state. Indeed cotunneling spectroscopy has been used to investigate electronic, vibrational and magnetic excitations in nanostructures such as a-few-electron semiconductor quantum dots,⁵³ carbon nanotube quantum dots,^{54,55} metallic carbon nanotubes,⁵⁶ and single-molecule junctions.⁵⁷⁻⁵⁹

At this point, before analyzing the transport results of our model, it is useful to make a connection with inelastic electron tunneling spectroscopy (IETS), studied for example by electron tunneling from a scanning tunneling spectroscopy (STM) tip through a molecule adsorbed on a surface^{60,61}. The reader familiar with IETS easily recognizes that the differential conductance versus applied voltage for this case is very similar to the cotunneling conductance of Coulomb blockade. This similarity is not accidental: the physics is essentially the same in both cases, since it involves the coherent electron tunneling through a finite system, whose internal degrees of freedom (e.g., vibrational, magnetic and electronic) can be excited by the process. The mathematical formulation of the problem is very similar in the two cases. There is one noticeable difference. In IETS by STM the coupling between the molecule and the (conducting) substrate is much stronger than the coupling between the STM tip and the molecule. Therefore typical IETS setups can be viewed as strongly asymmetric Coulomb-blockade systems, when these are studied in the cotunneling regime.

These considerations suggest an alternative way to investigate the spin-electric coupling in triangular MMs via quantum transport. In the setup of Fig. 6 we can imagine that transport through the MM occurs between the STM and the substrate, on which the MM is placed. Now the gates

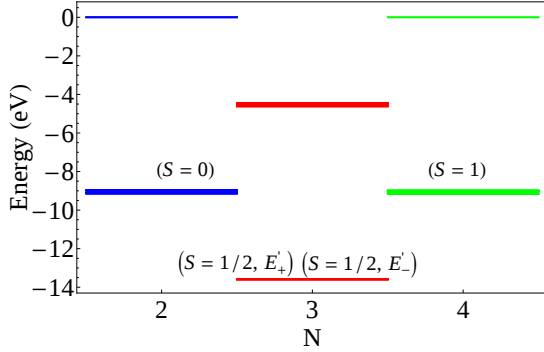


FIG. 7. (Color online) Low-energy spectrum of the triangular molecular magnet described by the Hubbard model, Eq. (8), for different charge states or electron filling, $N = 2, 3, 4$. Here the Hubbard model parameters, $t = -0.051$, $U = 9.06$, $\lambda_{\text{SOI}} = 0.0004$ (all in eV), are taken from first-principles calculations³⁴ for the $\{Cu_3\}$ molecular magnet. A gate voltage $V_g = U/2$ has been added to rigidly shift the spectrum of the system for a given N . The total spin of the ground state (GS) for the different charge states is indicated in parenthesis. The GS for the $N = 3$ -particle system corresponds to the chiral states, $E'_{\pm}$, defined in Eq. (16).

and leads constructed on the surface could provide the external electric field responsible for the spin-electric tunneling. For this purpose the plane of the triangular MM should be parallel to the surface of the substrate. In this case the detection and coherent manipulation of the low-energy chiral states of the MM would occur by means of IETS.

IV. RESULTS AND DISCUSSION

We now discuss quantum transport for the setup of Fig. 6. We first construct the relevant low-energy many-body states for the charge states containing $N = 2, 3, 4$ electrons. For this purpose we use the Hubbard model introduced in Sec. II. The parameters of the model are taken from the first-principles studies on the $\{Cu_3\}$ triangular molecular magnet (MM) by Ref. 34. We have $t = -51$ meV, $U = 9.06$ eV, $\lambda_{\text{SOI}} = 0.4$ meV. The model is solved exactly for $N = 2, 3, 4$. We label the many-body states with their electron number N (the charge state), total spin S and z -component of the total spin S_z .⁶² In case of additional degeneracy, we will use additional quantum numbers to specify the states, e.g., for the chiral degeneracy for the $N = 3$ ground state (GS), we will add $E'_{\pm}$.

The low-energy levels for the three contiguous charge states are shown in Fig. 7. To the energies calculated with the Hubbard model, we have added a gate voltage term $-eV_g N = -U/2 N$, which shifts rigidly the spectra of the different charge states with respect to each other. This

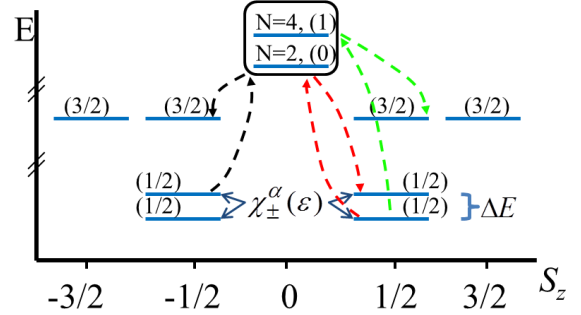


FIG. 8. (Color online). Schematic energy diagram of a triangular molecular magnet in the presence of an external electric field ε . Only the ground state (GS) of the $N = 2, 3, 4$ -particle system and the lowest excited states of the $N = 3$ system are included. The numbers in parenthesis corresponds to the total spin S . The electric field lifts the $N = 3$ GS degeneracy, and mixes the chiral states defined in Eq. (16). The “mixed chiral states”, are now labeled by $\chi^{\alpha}_{\pm}$, with χ^{α}_{-} being the GS. The GS splitting ΔE is linear in ε at low fields. Here we have used the same parameters of Fig. 7, plus $ea\varepsilon = 0.487$ eV, and $d_{EE\varepsilon} = 0.1ea\varepsilon$. The electric field is applied in the plane of the triangle, perpendicularly to line joining vertexes 1 and 2 of the triangle. Also shown in the figure with dashed-colored lines are allowed inelastic cotunneling transitions, occurring via $N = 2, 4$ virtual ground states, 2_0 and 4_0 , respectively. Red, black and green dashed lines correspond to transitions: $\chi_{-} \leftrightarrow \chi_{+}$ (ΔE), $\chi_{+} \leftrightarrow S = 3/2$ and $\chi_{-} \leftrightarrow S = 3/2$, respectively.

choice makes the spectra of the $N = 2$ and $N = 4$ charge states more symmetric with respect to the $N = 3$ states. We will also use this value of the gate voltage below, in the study of cotunneling transport, to make sure that the system is stable in the middle of the $N = 3$ Coulomb diamond.

For the present choice of the Hubbard parameters, these states are well described by the perturbative analysis of Sec. II. As discussed there, the GS for the $N = 3$ charge state (lowest middle line) is four-fold degenerate, and it corresponds to the states defined in Eq. (16). In Fig. 7 the same line denotes the position of the $S = 3/2$ excited state, whose separation from the GS is not visible on this energy scale.

We now consider the presence of a strong and localized electric field, generated, for example, by a scanning tunneling spectroscopy (STM) tip positioned nearby the MM. We will consider values of ε up to a maximum equal $0.1 \text{ V/\AA}$, which can be easily attained with a STM.^{63,64} For a $\{Cu_3\}$ MM, the distance between magnetic ions is $a = 4.87 \text{ \AA}$. For a spin-electric coupling strength $d = ea$, which is the maximum value estimated in Ref. 15, the energy scale $ea\varepsilon$ is equal to 0.487 eV when $\varepsilon = 0.1 \text{ V/\AA}$. As discussed in Sec. II, we model the effect of the electric field in the Hubbard approach via the pa-

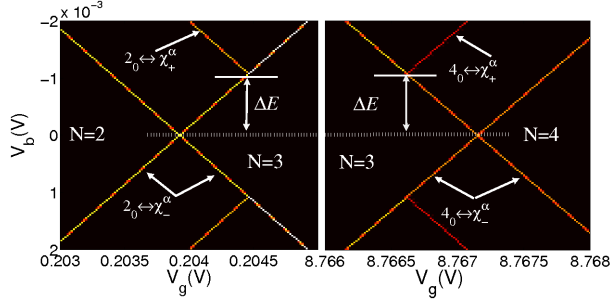


FIG. 9. (Color online) Differential conductance as a function of the bias and gate voltages in the sequential tunneling regime (stability diagram), showing the Coulomb diamonds for three contiguous charge states $N = 2, 3, 4$. Only the corners of the diamonds are shown. The arrows indicate the electron transitions responsible for peaks in the conductance. States are labeled following the notation of Fig. 8. The calculations are done for a symmetric device at temperature $T \sim 10^{-2} K$ ($k_B T \sim 0.001 \text{ meV}$). The parameters for the Hubbard model are the same of those in Fig. 8, A local electric field $\varepsilon = 0.1 \text{ V/\AA}$, is also included, causing a spin-electric coupling of the $N = 3$ chiral states and a ground state splitting ΔE .

rameters a , d_{EE} , d_{AE} entering the single-particle Hamiltonians in Eqs. (25) and (28). Here we take $d_{EE} = 0.1ea$ and $d_{AE} = 0$. The effect of the field on the low-energy spectrum of the MM is shown in Fig. 8, with the expected splitting and mixing of the GS chiral states for the $N = 3$ charge state. In the absence of spin orbit interaction (SOI) the “mixed chiral states” $|\chi_-^\alpha(\varepsilon)\rangle$ and $|\chi_+^\alpha(\varepsilon)\rangle$ (with $|\chi_-^\alpha(\varepsilon)\rangle$ being the GS) are still spin ($\alpha = \pm 1/2$) degenerate. As we saw, their splitting $\Delta E(\varepsilon)$ is proportional to ε . It is interesting to note that, the (small) spin-orbit coupling given in Eq. (29), mixes a little bit $|\chi_-^\alpha(\varepsilon)\rangle$ and $|\chi_+^\alpha(\varepsilon)\rangle$. However, since the effect is the same for $\alpha = \pm 1/2$, the double degeneracy of the GS and the first excited state is preserved, and the splitting remains of the order of $\Delta E(\varepsilon)$.

Shown on the same figure are also the four-fold degenerate ($N = 3$, $S = 3/2$) excited state and the $N = 2$ and $N = 4$ GS, having spin $S = 0$ and $S = 1$ respectively. The $N = 2(4)$ GS has total spin $S = 0(1)$ and spin projection $S_z = 0(0)$. The rest of the energy spectrum is not shown in Fig. 8.

In Fig. 9 we plot the Coulomb blockade stability diagram, that is, the differential conductance in the sequential tunneling regime as a function of bias and gate voltages. The calculations are done for a symmetric device, where the capacitances and tunneling resistances for the two junctions are the same. The temperature is taken to be $T \sim 10^{-2} K$ ($k_B T \sim 0.001 \text{ meV}$). The calculations are done for the parameters of Fig. 8, and an electric field $\varepsilon = 0.1 \text{ V/\AA}$ is included, generating a GS splitting ΔE for the $N = 3$ charge state.

The picture displays familiar Coulomb diamonds for the three contiguous charge states $N = 2, 3, 4$, inside which the current is zero. The lines delimiting these diamonds represent the onset of tunneling current, where the conductance has peaks. They correspond to real transitions between states of two contiguous charge states $N \rightarrow N \pm 1$. The first lines where this happens involve the transition between the corresponding GSs. Other lines, parallel to these, involve transitions between excited states, which become occupied out of equilibrium. We do not include any energy or spin relaxation mechanism in these calculations.

We now consider transport in the cotunneling regime. In Fig. 10 we plot the differential conductance as a function of the bias voltage V_b , for $V_g = U/2$, which locates the system in the middle of $N = 3$ Coulomb diamond, that is, deep inside the Coulomb blockade regime. Here the sequential tunneling current is suppressed, and transport is entirely due to cotunneling. The conductance is nonzero even at zero bias, due to elastic cotunneling. At $V_b \approx 1.1 \text{ meV}$, the conductance has a first step, indicated by the red dashed line. The step signals the onset of inelastic cotunneling, which takes place when the bias voltage provides enough energy for the final occupation of the lowest excited state of the $N = 3$ charge state ($N = 3, \chi_+^\alpha$), via the virtual transition from the ($N = 3, \chi_-^\alpha$) GS to the ($N = 2, S = 0$), ($N = 4, S = 1$) GSs. Therefore, the width of this first step provides a direct estimate of the energy splitting between the mixed chiral states, ($N = 3, \chi_+^\alpha$) and ($N = 3, \chi_-^\alpha$), caused by the spin-electric coupling. Increasing further the bias, other two cotunneling channels open up, causing the appearance of two other steps in the conductance. The first one, quite small, indicated by the black dashed line, is related with the first occupation of the ($N = 3, S = 3/2$) excited state, which occurs via the virtual transition from the ($N = 3, \chi_+^\alpha$) excited state to the ($N = 2, S = 0$), ($N = 4, S = 1$) GSs. Note that the state ($N = 3, \chi_+^\alpha$) is already occupied because of the first inelastic cotunneling transition. The second (higher) step, indicated by a green dashed line, is again due to the occupation of the ($N = 3, S = 3/2$) as a final state, but though the virtual transition from the ($N = 3, \chi_-^\alpha$) GS to the ($N = 2, S = 0$), ($N = 4, S = 1$) GSs.

The cotunneling conductance pattern depends on the external electric field ε . In Fig. 11 we plot the conductance as function of the external electric field, ε and bias voltage, V_b . As expected, the value of the voltage where the first inelastic step occurs increases with the field. Variations of the position of the other two inelastic steps in the conductance as a function of ε are also visible: at low fields, where the splitting of the chiral GS vanishes, the other two inelastic steps involving the

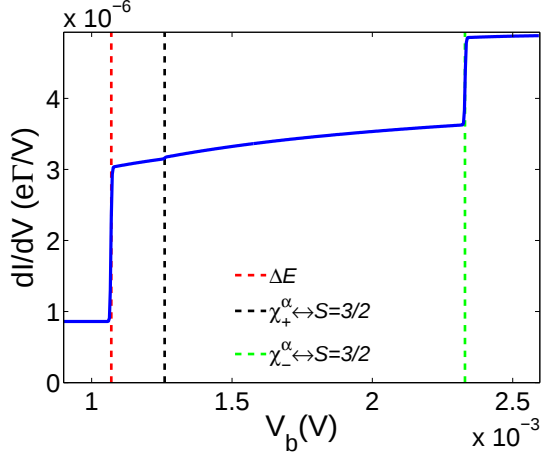


FIG. 10. (Color online) Cotunneling differential conductance as a function of the bias voltage for parameters as in Fig. 7. The states involved are labeled as in Fig. 8. At low voltage, transport is through elastic cotunneling. The red-dashed line corresponds to the first onset of inelastic cotunneling, due to the occupation of the lowest excited state ($N = 3, \chi_+^\alpha$), through a virtual transition ($N = 3, \chi_-^\alpha$) ground state (GS) $\rightarrow (N = 2, S = 0), (N = 4, S = 1)$ GSs. The black-dashed line and green-dashed line indicate inelastic cotunneling steps caused by the final occupation of the ($N = 3, S = 3/2$) excited state via the virtual transitions from ($N = 3, \chi_\pm^\alpha$) to the ($N = 2, S = 0$), ($N = 4, S = 1$) GSs.

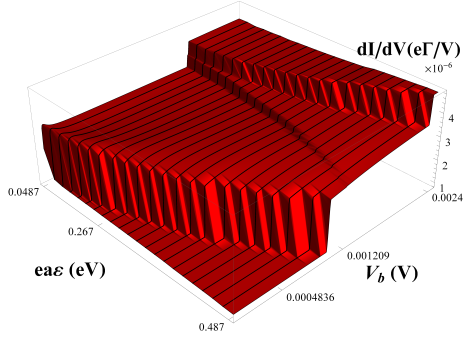


FIG. 11. Cotunneling differential conductance as a function of the bias voltage and the local electric field triggering the spin-electric coupling.

($N = 3, S = 3/2$) excited state occur at the same bias. Surprisingly, the height of the inelastic steps is *not* strongly affected by the electric field. The only exception is the second step, whose height becomes very small at the maximum value of ε , as also shown in Fig. 10.

In Fig. 12 we plot ΔE , extracted from the position of first inelastic step, as a function of ε . A polynomial fitting of ΔE vs. ε finds, besides a quadratic contribution due to an induced electric dipole moment, a linear term, which dominates at low fields, and it is the landmark of the (linear) spin-electric coupling. Interestingly, the ex-

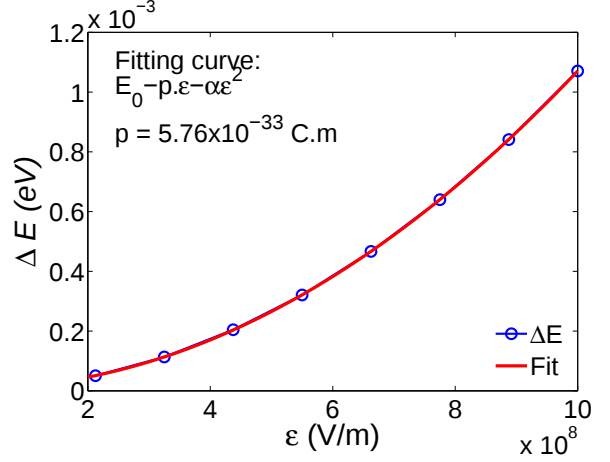


FIG. 12. Energy splitting of the $N = 3$ chiral ground state, ΔE , caused by the spin-electric coupling, as a function of the external electric field. The values of ΔE correspond to the position of the first conductance step in Fig. 11. The fitting curve contains a linear term proportional to a dipole moment $p = 5.76 \cdot 10^{-33}$ C m, in agreement with the first-principles calculations on $\{Cu_3\}$ molecular magnet of Ref. 21.

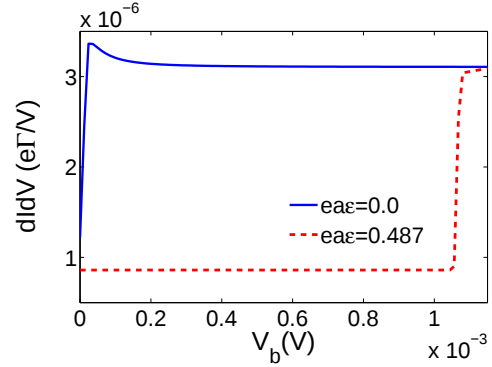


FIG. 13. (Color online) Cotunneling differential conductance versus bias voltage with (dashed red line) and without (blue solid line) external electric field, causing the spin-electric coupling. Here we have used the same parameters of Fig. 8.

tracted value of the proportionality coefficient of the linear term, i.e. the “electric dipole moment” $p = d/\sqrt{2}$, is equal to $5.76 \cdot 10^{-33}$ C m, which is consistent with the value found previously by *ab-initio* methods for $\{Cu_3\}$ molecular magnet.²¹ This indicates that our choice of the spin-electric parameter $d_{EE} = 0.1ea$ (see Eqs. (24) and (25)) is in the right ballpark. In principle, the curve plotted in Fig. 12 can be directly extracted from experimental measurements of the conductance in the cotunneling regime. From this curve, the strength of electric dipole moment d can be estimated.

The cotunneling conductance for both $\varepsilon = 0$ (blue line) and $\varepsilon = 0.1$ V/Å (red dashed line) is

plotted in Fig. 13. At zero field, the splitting of the $N = 3$ GS, controlling the onset of inelastic cotunneling, is brought about only by the SOI-induced Dzyaloshinskii-Moriya interaction, which splits the chiral states without mixing them. This splitting is predicted to be very small, both experimentally¹⁵ ($\Delta_{\text{SOI}} = 0.04$ meV) and theoretically ($\Delta_{\text{SOI}} = 0.02$ meV)³⁴. The value extracted from the cotunneling conductance of Fig. (13) is consistent with this estimate. A measurement of this splitting from cotunneling experiments is also in principle possible but probably very challenging. The value of the elastic cotunneling conductance is slightly larger when the ϵ -field is absent than in the presence of the field. However value of the inelastic conductance is the same with and without field. The fact that inelastic cotunneling sets in at very different thresholds with and without field suggests the possibility of using this system as a switching device, which can be controlled electrically, possibly by a time-dependent field.

V. CONCLUSIONS

In summary, we have carried out a theoretical study of quantum transport through an antiferromagnetic triangular molecular magnet (MM), in a single-electron transistor setup. The interplay of spin frustration and lack of inversion symmetry in this MM is responsible for the existence of an efficient spin-electric coupling, which can affect the non-linear transport regime. When a strong localized electric field is applied to the molecule, the spin-electric coupling causes a splitting between the two doubly-degenerate spin chiral states that compose the ground state of the MM. We have shown that this energy splitting and, consequently the strength of the spin-coupling, should be directly accessible through experiments by measuring the inelastic cotunneling conductance in the Coulomb blockade regime. Both single-electron transistors (SETs) used in molecular spintronics and inelastic electron tunneling spectroscopy (IETS) of molecules on surfaces addressed with a STM could be employed to study this effect.

Our theoretical approach was based on a Hub-

bard model,^{15,18} where the spin-electric coupling can be described in terms of a few microscopic parameters derivable from first-principles calculations. We have shown that the value of the strength of spin-electric coupling estimated from tunneling transport is consistent with the value calculated by first-principles methods.²¹

Antiferromagnetic molecules, like the one considered here, characterized by ground states composed of chiral pairs of spin-1/2 doublets, could be used to create pairs of quasi-degenerate qbits. The possibility of coherently coupling these two qbits electrically and detecting their quantum superposition state in electronic transport is an interesting topic that should further investigated.

The effect of an external magnetic field, not considered in this paper, can be used for gaining full control of the ground-state manifold. Furthermore, higher excited states of the system can play a role as auxiliary states employed to perform quantum gates. As we have shown in our study of the cotunneling conductance (see Fig. 11), these higher states can also be manipulated electrically and brought closer to or further apart from the ground-state manifold. One important issue that we have not discussed in this work is the effect of spin relaxation on transport. This certainly plays a crucial role in determining the robustness of the coherent superposition induced by the electric field.

ACKNOWLEDGMENT

We would like to thank D. Loss and D. Stepanenko for several important discussions and clarifications on the spin-electric coupling in molecular magnets, and M. Islam for an ongoing collaboration on the same subject. We would like to thank Dr. Magnus Paulsson for his help in developing the codes used in this work. This work was supported by the School of Computer Science, Physics and Mathematics at Linnaeus University, the Swedish Research Council under Grants No: 621-2007-5019 and 621-2010-3761, and the Nord-Forsk research network 080134 "Nanospintronics: theory and simulations".

Appendix A: Explicit derivation of Eq. (54)

Here we demonstrate the Eq. (54). We study the transition rates up to four order. The transition rate from state $|j\rangle|n\rangle$ to $|j'\rangle|n'\rangle$ with one electron tunneling from lead α to the lead α' is given by

$$\Gamma_{\alpha\alpha'}^{nj;n'j'} = \frac{2\pi}{\hbar} \left| \langle j'| \langle n'| \mathcal{H}^T \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} \mathcal{H}^T |n\rangle |j\rangle \right|^2 \delta(E_{j'n'} - E_{jn}),$$

where $E_{j'n'}$ and E_{jn} are the energies of the final and initial states, respectively. $\mathcal{H}_T = \sum_{\alpha=L,R} t_\alpha \sum_{\mathbf{k}\sigma} \left(a_{\alpha\mathbf{k}\sigma}^\dagger c_\sigma + c_\sigma^\dagger a_{\alpha\mathbf{k}\sigma} \right)$ is the tunneling Hamiltonian Eq. (36) with $T_{km\alpha}^{L/R} = t_\alpha$. $\mathcal{H}_0 =$

$\mathcal{H}_{mol} + \mathcal{H}_{leads}$ and η is a positive infinitesimal number. Here $|j'\rangle |n'\rangle = a_{\alpha' \mathbf{k}' \sigma'}^\dagger a_{\alpha \mathbf{k} \sigma} |j\rangle |n\rangle$. $|j\rangle$ ($|n\rangle$) refers to the equilibrium state of the left and right Fermi sea (molecule). The total cotunneling rates for transitions that involve virtual transitions between two n, n' -occupied molecule states are then given by

$$\begin{aligned}
\Gamma_{\alpha\alpha'}^{nj;n'j'} &= \frac{2\pi}{\hbar} \sum_{\mathbf{k}\mathbf{k}'\sigma\sigma'} \left| \langle j | \langle n' | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} \sum_{\alpha'''} t_{\alpha'''}^* \sum_{\mathbf{k}''\sigma''} \left(a_{\alpha'''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} + c_{\sigma''}^\dagger a_{\alpha'''\mathbf{k}''\sigma''} \right) \right. \\
&\quad \times \left. \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} \sum_{\alpha''} t_{\alpha''} \sum_{\mathbf{k}''\sigma''} \left(a_{\alpha''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} + c_{\sigma''}^\dagger a_{\alpha''\mathbf{k}''\sigma''} \right) |n\rangle |j\rangle \right|^2 \delta(E_{j'n'} - E_{jn}) \\
&= \frac{2\pi}{\hbar} \sum_{\mathbf{k}\mathbf{k}'\sigma\sigma'} \left| \langle j | \langle n' | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} \sum_{\alpha'''\mathbf{k}''\sigma''} \sum_{\alpha''\mathbf{k}''\sigma''} t_{\alpha'''}^* t_{\alpha''} \right. \\
&\quad \times \left(\underbrace{a_{\alpha'''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} a_{\alpha''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} + a_{\alpha'''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} c_{\sigma''}^\dagger a_{\alpha''\mathbf{k}''\sigma''}}_{= 0, n-2 \text{ states}} \right. \\
&\quad \left. \left. + c_{\sigma''}^\dagger a_{\alpha'''\mathbf{k}''\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} a_{\alpha''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} + c_{\sigma''}^\dagger a_{\alpha'''\mathbf{k}''\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} c_{\sigma''}^\dagger a_{\alpha''\mathbf{k}''\sigma''} \right) \right. \\
&\quad \left. \times |n\rangle |j\rangle \right|^2 \delta(E_{j'n'} - E_{jn}) \\
\Gamma_{\alpha\alpha'}^{nj;n'j'} &= \frac{2\pi}{\hbar} \sum_{\mathbf{k}\mathbf{k}'\sigma\sigma'} \left| \langle j | \langle n' | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} \sum_{\alpha'''\mathbf{k}''\sigma''} \sum_{\alpha''\mathbf{k}''\sigma''} t_{\alpha'''}^* t_{\alpha''} \left\{ c_{\sigma''}^\dagger a_{\alpha'''\mathbf{k}''\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} a_{\alpha''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} \right. \right. \\
&\quad \left. \left. + a_{\alpha'''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} c_{\sigma''}^\dagger a_{\alpha''\mathbf{k}''\sigma''} \right\} |n\rangle |j\rangle \right|^2 \delta(E_{j'n'} - E_{jn}) \\
&= \frac{2\pi}{\hbar} \sum_{\mathbf{k}\mathbf{k}'\sigma\sigma'} \left| \sum_{\alpha'''\mathbf{k}''\sigma''} \sum_{\alpha''\mathbf{k}''\sigma''} t_{\alpha'''}^* t_{\alpha''} \left\{ \right. \right. \\
&\quad \left. \langle j | \langle n' | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} c_{\sigma''}^\dagger a_{\alpha'''\mathbf{k}''\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} a_{\alpha''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} |n\rangle |j\rangle \right. \\
&\quad \left. \left. + \langle j | \langle n' | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} a_{\alpha'''\mathbf{k}''\sigma''}^\dagger c_{\sigma''} \frac{1}{E_{jn} - \mathcal{H}_0 + i\eta} c_{\sigma''}^\dagger a_{\alpha''\mathbf{k}''\sigma''} |n\rangle |j\rangle \right\} \right|^2 \delta(E_{j'n'} - E_{jn}) \quad (\text{A1})
\end{aligned}$$

Here n and n' are states with the same number of particles. Now we take a look at the numerator terms

$$\begin{aligned}
\langle j | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} a_{\alpha'''\mathbf{k}''\sigma''}^\dagger a_{\alpha''\mathbf{k}''\sigma''} | j \rangle &= - \langle j | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha'''\mathbf{k}''\sigma''}^\dagger a_{\alpha' \mathbf{k}' \sigma'} a_{\alpha''\mathbf{k}''\sigma''} | j \rangle \\
&= -f(\varepsilon - \mu_\alpha) \delta_{\alpha\alpha'''} \delta_{\mathbf{k}\mathbf{k}''} \delta_{\sigma\sigma''} \\
&\quad \times (1 - f(\varepsilon + \varepsilon_n - \varepsilon_{n'} - \mu_{\alpha'})) \delta_{\alpha'\alpha'''} \delta_{\mathbf{k}'\mathbf{k}''} \delta_{\sigma'\sigma''}
\end{aligned}$$

and

$$\begin{aligned}
\langle j | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} a_{\alpha'''\mathbf{k}''\sigma''}^\dagger a_{\alpha''\mathbf{k}''\sigma''} | j \rangle &= \langle j | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} \left(\delta_{\alpha'''\mathbf{k}''\sigma''} a_{\alpha''\mathbf{k}''\sigma''}^\dagger - a_{\alpha''\mathbf{k}''\sigma''}^\dagger \delta_{\alpha'''\mathbf{k}''\sigma''} \right) | j \rangle \\
&= - \langle j | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha' \mathbf{k}' \sigma'} a_{\alpha''\mathbf{k}''\sigma''}^\dagger a_{\alpha'''\mathbf{k}''\sigma''} | j \rangle \\
&= \langle j | a_{\alpha \mathbf{k} \sigma}^\dagger a_{\alpha''\mathbf{k}''\sigma''} | j \rangle \langle j | a_{\alpha' \mathbf{k}' \sigma'} a_{\alpha'''\mathbf{k}''\sigma''}^\dagger | j \rangle \\
&= f(\varepsilon - \mu_\alpha) \delta_{\alpha\alpha''} \delta_{\mathbf{k}\mathbf{k}''} \delta_{\sigma\sigma''} \\
&\quad (1 - f(\varepsilon + \varepsilon_n - \varepsilon_{n'} - \mu_{\alpha'})) \delta_{\alpha'\alpha'''} \delta_{\mathbf{k}'\mathbf{k}''} \delta_{\sigma'\sigma''}
\end{aligned}$$

Here we have used a Taylor series expansion on the operator $1/(E_{jn} - H_0) = (1/E_{jn}) \sum_{l=0}^{\infty} (H_0/E_{jn})^l$.

Taking into account last delta rules, we have

$$\langle n' | c_{\sigma''}^\dagger c_{\sigma'} | n \rangle = \sum_{n''} \langle n' | c_{\sigma'}^\dagger | n'' \rangle \langle n'' | c_{\sigma'} | n \rangle = \sum_{n''} (\langle n'' | c_{\sigma'} | n \rangle)^\dagger \langle n'' | c_{\sigma'} | n \rangle = \sum_{n''} A_{n''n'}^{\sigma*} A_{n''n}^{\sigma'}$$

and

$$\langle n' | c_{\sigma'} c_{\sigma}^\dagger | n \rangle = \sum_{n''} \langle n' | c_{\sigma'} | n'' \rangle \langle n'' | c_{\sigma}^\dagger | n \rangle = \sum_{n''} \langle n' | c_{\sigma'} | n'' \rangle (\langle n | c_{\sigma} | n'' \rangle)^\dagger = \sum_{n''} A_{n'n''}^{\sigma'} A_{nn''}^{\sigma*}$$

where $A_{n'n''}^{\sigma'} = \langle n' | c_{\sigma'} | n'' \rangle$ and $A_{nn''}^{\sigma*} = \langle n'' | c_{\sigma}^\dagger | n \rangle$. Here n'' represents a intermediate state.

Thus Eq. (A1) becomes

$$\begin{aligned} \Gamma_{\alpha\alpha'}^{nj;n'j'} &= \frac{2\pi}{\hbar} \sum_{\mathbf{k}\mathbf{k}'\sigma\sigma'} \left| \sum_{\alpha'''\mathbf{k}'''\sigma'''} \sum_{\alpha''\mathbf{k}''\sigma''} t_{\alpha'''}^* t_{\alpha''} \left\{ \right. \right. \\ &\quad - \langle j | \langle n' | a_{\alpha\mathbf{k}\sigma}^\dagger a_{\alpha'\mathbf{k}'\sigma'} a_{\alpha'''\mathbf{k}'''\sigma'''} c_{\sigma'''}^\dagger \frac{1}{\varepsilon_{n'} - \varepsilon_{n''} - \varepsilon + i\eta} c_{\sigma''} | n \rangle a_{\alpha''\mathbf{k}''\sigma''}^\dagger | j \rangle \\ &\quad \left. \left. + \langle j | \langle n' | a_{\alpha\mathbf{k}\sigma}^\dagger a_{\alpha'\mathbf{k}'\sigma'} a_{\alpha'''\mathbf{k}'''\sigma'''} c_{\sigma'''}^\dagger \frac{1}{\varepsilon_n - \varepsilon_{n''} + \varepsilon + i\eta} c_{\sigma''}^\dagger | n \rangle a_{\alpha''\mathbf{k}''\sigma''} | j \rangle \right\} \right|^2 \delta(E_{j'n'} - E_{jn}) \\ \Gamma_{\alpha\alpha'}^{n;n'} &= 2 |t_\alpha|^2 |t_{\alpha'}|^2 \sum_{\sigma\sigma'} \nu_\alpha(\sigma) \nu_{\alpha'}(\sigma') \int d\varepsilon f(\varepsilon - \mu_\alpha) (1 - f(\varepsilon + \varepsilon_n - \varepsilon_{n'} - \mu_{\alpha'})) \\ &\quad \times \left| \sum_{n''} \left\{ \frac{A_{n''n'}^{\sigma*} A_{n''n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_{n''} + i\eta} + \frac{A_{n'n''}^{\sigma'} A_{nn''}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_{n''} + i\eta} \right\} \right|^2 \\ &= \sum_{\sigma\sigma'} \gamma_\alpha^\sigma \gamma_{\alpha'}^{\sigma'} \int d\varepsilon f(\varepsilon - \mu_\alpha) (1 - f(\varepsilon + \varepsilon_n - \varepsilon_{n'} - \mu_{\alpha'})) \\ &\quad \times \underbrace{\left| \sum_{n''} \left\{ \frac{A_{n''n'}^{\sigma*} A_{n''n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_{n''} + i\eta} + \frac{A_{n'n''}^{\sigma'} A_{nn''}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_{n''} + i\eta} \right\} \right|^2}_Q \end{aligned} \quad (\text{A2})$$

Appendix B: Explicit derivation of Eq. (55)

The absolute value in Eq. (A2) can be written as

$$\begin{aligned} Q &= \left| \sum_{n''} \left\{ \frac{A_{n''n'}^{\sigma*} A_{n''n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_{n''} + i\eta} + \frac{A_{n'n''}^{\sigma'} A_{nn''}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_{n''} + i\eta} \right\} \right|^2 \\ &= \left(\frac{A_{1n}^{\sigma*} A_{1n'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_1 - i\eta} + \frac{A_{n1}^{\sigma'} A_{n'1}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_1 - i\eta} + \frac{A_{2n}^{\sigma*} A_{2n'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_2 - i\eta} + \frac{A_{n2}^{\sigma'} A_{n'2}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_2 - i\eta} \right. \\ &\quad \left. + \frac{A_{3n}^{\sigma*} A_{3n'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_{n''} - i\eta} + \frac{A_{n3}^{\sigma'} A_{n'3}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_3 - i\eta} \right) \\ &\quad \times \left(\frac{A_{1n'}^{\sigma*} A_{1n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_1 + i\eta} + \frac{A_{n'1}^{\sigma'} A_{n1}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_1 + i\eta} + \frac{A_{2n'}^{\sigma*} A_{2n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_2 + i\eta} + \frac{A_{n'2}^{\sigma'} A_{n2}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_2 + i\eta} \right. \\ &\quad \left. + \frac{A_{3n'}^{\sigma*} A_{3n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_{n''} + i\eta} + \frac{A_{n'3}^{\sigma'} A_{n3}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_3 + i\eta} \right) \end{aligned}$$

$$\begin{aligned}
Q = & \sum_k \left(\frac{(A_{kn'}^{\sigma*} A_{kn}^{\sigma'})^2}{(\varepsilon - \varepsilon_{n'} + \varepsilon_k)^2 + \eta^2} + \frac{(A_{n'k}^{\sigma'} A_{nk}^{\sigma*})^2}{(\varepsilon + \varepsilon_n - \varepsilon_k)^2 + \eta^2} \right) \\
& + 2Re \sum_q \sum_{k < q} \left(\frac{A_{qn'}^{\sigma*} A_{qn}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_q + i\eta} \frac{A_{kn'}^{\sigma*} A_{kn}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_k - i\eta} + \frac{A_{n'q}^{\sigma'} A_{nq}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_q + i\eta} \frac{A_{n'k}^{\sigma'} A_{nk}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_k - i\eta} \right) \\
& + 2Re \sum_q \sum_k \left(\frac{A_{kn'}^{\sigma*} A_{kn}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_q - i\eta} \frac{A_{n'k}^{\sigma'} A_{nk}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_k - i\eta} \right)
\end{aligned}$$

Thus Eq. (54) becomes

$$\begin{aligned}
\Gamma_{\alpha\alpha'}^{n;n'} &= \sum_{\sigma\sigma'} \gamma_{\alpha}^{\sigma} \gamma_{\alpha'}^{\sigma'} \int d\varepsilon f(\varepsilon - \mu_{\alpha}) (1 - f(\varepsilon + \varepsilon_n - \varepsilon_{n'} - \mu_{\alpha'})) \\
&\quad \times \left| \sum_{n''} \left\{ \frac{A_{n''n'}^{\sigma*} A_{n''n}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_{n''} + i\eta} + \frac{A_{n'n''}^{\sigma'} A_{nn''}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_{n''} + i\eta} \right\} \right|^2 \\
&= \sum_{\sigma\sigma'} \gamma_{\alpha}^{\sigma} \gamma_{\alpha'}^{\sigma'} \int d\varepsilon f(\varepsilon - \mu_{\alpha}) (1 - f(\varepsilon + \varepsilon_n - \varepsilon_{n'} - \mu_{\alpha'})) \\
&\quad \times \left[\sum_k \left(\frac{(A_{kn'}^{\sigma*} A_{kn}^{\sigma'})^2}{(\varepsilon - \varepsilon_{n'} + \varepsilon_k)^2 + \eta^2} + \frac{(A_{n'k}^{\sigma'} A_{nk}^{\sigma*})^2}{(\varepsilon + \varepsilon_n - \varepsilon_k)^2 + \eta^2} \right) \right. \\
&\quad + 2Re \sum_q \sum_{k < q} \left(\frac{A_{qn'}^{\sigma*} A_{qn}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_q + i\eta} \frac{A_{kn'}^{\sigma*} A_{kn}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_k - i\eta} + \frac{A_{n'q}^{\sigma'} A_{nq}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_q + i\eta} \frac{A_{n'k}^{\sigma'} A_{nk}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_k - i\eta} \right) \\
&\quad \left. + 2Re \sum_q \sum_k \left(\frac{A_{kn'}^{\sigma*} A_{kn}^{\sigma'}}{\varepsilon - \varepsilon_{n'} + \varepsilon_q - i\eta} \frac{A_{n'k}^{\sigma'} A_{nk}^{\sigma*}}{\varepsilon + \varepsilon_n - \varepsilon_k - i\eta} \right) \right] \\
\Gamma_{\alpha\alpha'}^{n;n'} &= \sum_{\sigma\sigma'} \gamma_{\alpha}^{\sigma} \gamma_{\alpha'}^{\sigma'} \int d\varepsilon f(\varepsilon - E_1) (1 - f(\varepsilon - E_2)) \\
&\quad \times \left[\sum_k \frac{A^2}{(\varepsilon - \varepsilon_{ak})^2 + \eta^2} \quad (\text{Integral type J}) \right. \\
&\quad + \sum_k \frac{B^2}{(\varepsilon - \varepsilon_{bk})^2 + \eta^2} \quad (\text{Integral type J}) \\
&\quad + 2Re \sum_q \sum_{k < q} \frac{A_k}{\varepsilon - \varepsilon_{ak} + i\eta} \frac{A_q}{\varepsilon - \varepsilon_{aq} - i\eta} \quad (\text{Integral type I}) \\
&\quad + 2Re \sum_q \sum_{k < q} \frac{B_k}{\varepsilon - \varepsilon_{bk} + i\eta} \frac{B_q}{\varepsilon - \varepsilon_{bq} - i\eta} \quad (\text{Integral type I}) \\
&\quad \left. + 2Re \sum_q \sum_k \frac{A_k}{\varepsilon - \varepsilon_{ak} + i\eta} \frac{B_q}{\varepsilon - \varepsilon_{bq} - i\eta} \right] \quad (\text{Integral type I})
\end{aligned}$$

where $A_k = A_{kn'}^{\sigma*} A_{kn}^{\sigma'}$, $B_k = A_{n'k}^{\sigma'} A_{nk}^{\sigma*}$, $\varepsilon_{ak} = \varepsilon_{n'} - \varepsilon_k$, $\varepsilon_{bk} = \varepsilon_k - \varepsilon_n$, $E_1 = \mu_{\alpha}$ and $E_2 = \mu_{\alpha'} + \varepsilon_{n'} - \varepsilon_n$.

Integral type I

$$\begin{aligned}
I(E_1, E_2, \varepsilon_1, \varepsilon_2) &= Re \int d\varepsilon f(\varepsilon - E_1) [1 - f(\varepsilon - E_2)] \frac{1}{\varepsilon - \varepsilon_1 - i\gamma} \frac{1}{\varepsilon - \varepsilon_2 + i\gamma} \\
&= \frac{n_B(E_2 - E_1)}{\varepsilon_1 - \varepsilon_2} Re \left\{ \psi \left(\frac{1}{2} + \frac{i\beta}{2\pi} [E_2 - \varepsilon_1] \right) - \psi \left(\frac{1}{2} - \frac{i\beta}{2\pi} [E_2 - \varepsilon_2] \right) \right. \\
&\quad \left. - \psi \left(\frac{1}{2} + \frac{i\beta}{2\pi} [E_1 - \varepsilon_1] \right) + \psi \left(\frac{1}{2} - \frac{i\beta}{2\pi} [E_1 - \varepsilon_2] \right) \right\} \quad (\text{B1})
\end{aligned}$$

Here ψ is the digamma function, n_B is the Bose function and $\beta = 1/k_B T$.

Integral type J

$$\begin{aligned} J(E_1, E_2, \varepsilon_1) &= \int d\varepsilon f(\varepsilon - E_1) [1 - f(\varepsilon - E_2)] \frac{1}{(\varepsilon - \varepsilon_1)^2 + \eta^2} \\ &= \frac{\beta}{2\pi} n_B(E_2 - E_1) \text{Im} \left\{ \psi' \left(\frac{1}{2} + \frac{i\beta}{2\pi} [E_2 - \varepsilon_1] \right) - \psi' \left(\frac{1}{2} + \frac{i\beta}{2\pi} [E_1 - \varepsilon_1] \right) \right\} \end{aligned} \quad (\text{B2})$$

Thus Eq. (B1) becomes

$$\begin{aligned} \Gamma_{\alpha\alpha'}^{n;n'} &= \sum_{\sigma\sigma'} \gamma_{\alpha}^{\sigma} \gamma_{\alpha'}^{\sigma'} \left[\sum_k (A^2 J(E_1, E_2, \varepsilon_{ak}) + B^2 J(E_1, E_2, \varepsilon_{bk})) \right. \\ &\quad + 2 \sum_q \sum_{k \neq q} (A_k A_q I(E_1, E_2, \varepsilon_{ak}, \varepsilon_{aq}) + B_k B_q I(E_1, E_2, \varepsilon_{bk}, \varepsilon_{bq})) \\ &\quad \left. + 2 \sum_q \sum_k A_k B_q I(E_1, E_2, \varepsilon_{ak}, \varepsilon_{bq}) \right] \end{aligned} \quad (\text{B3})$$

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